

Twist-Programmable Superconductivity in Spin-Orbit Coupled Bilayer Graphene

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The relative twist angle between layers of near-lattice-matched van der Waals materials is critical for the emergent correlated phenomena associated with moiré flat bands¹⁻³. However, the concept of angle rotation control is not exclusive to moiré superlattices in which electrons directly experience a twist-angle-dependent periodic potential. Instead, it can also be employed to induce programmable symmetry-breaking perturbations with the goal of stabilizing desired correlated states. Here, we experimentally demonstrate ‘moiréless’ twist-tuning of superconductivity together with other correlated orders in Bernal bilayer graphene proximitized by tungsten diselenide. The precise alignment between the two materials systematically controls the strength of the induced Ising spin-orbit coupling (SOC), profoundly altering the phase diagram. As Ising SOC is increased, superconductivity onsets at a higher displacement field and features a higher critical temperature, reaching up to 0.5 K. Within the main superconducting dome and in the strong Ising SOC limit, we find an unusual phase transition characterized by a nematic redistribution of holes among trigonally warped Fermi pockets and enhanced resilience to in-plane magnetic fields. The behavior of the superconducting phase is well captured by our theoretical model, which emphasizes the prominent role of interband interactions between Fermi pockets arising due to interaction-enhanced symmetry breaking. Moreover, we identify two additional superconducting regions, one of which descends from an inter-valley coherent normal state and exhibits a Pauli-limit violation ratio exceeding 40, among the highest for all known superconductors⁴⁻⁷. Our results provide essential insights into ultra-clean graphene-based superconductors and underscore

the potential of utilizing moiréless-twist engineering across a wide range of van der Waals heterostructures.

In a large electrical displacement field, the electronic bands of Bernal bilayer graphene (BLG) flatten out around the corners of the Brillouin zone, giving rise to various correlated phases that spontaneously break BLG symmetries^{4,8,9}. These correlated phases naturally compete with each other and, therefore, are highly sensitive to explicit symmetry-breaking perturbations. One way to induce such perturbations is by placing BLG adjacent to transition metal dichalcogenides such as tungsten diselenide (WSe₂). Due to a large mismatch of the unit cells, WSe₂ does not induce a moiré potential that is deep enough to renormalize the low-energy bands of BLG significantly. Yet, the SOC perturbations induced by WSe₂¹⁰⁻¹⁶ alter the phase diagram and remarkably enhance the otherwise exceedingly fragile superconductivity in BLG⁴, enabling superconductivity at zero magnetic field and boosting the critical temperature significantly¹⁷⁻¹⁹. However, the nature and the extent of this enhancement, and more generally, the impact of spin-orbit interaction on the correlated phase diagram of BLG and other graphene systems, remain elusive and experimentally underexplored.

Theoretically, the induced SOC is predicted to depend on the relative twist angle θ between WSe₂ and graphene^{16,20-23} (Fig. 1a). This dependence, however, has not been experimentally studied or utilized with systematic control. Here we employ this novel tuning knob to explore how Ising SOC modifies the correlated phases and emerging superconductivity in BLG. This approach offers several unique opportunities for exploring the properties of ultra-clean and highly tunable superconductors: (i) the strength of the induced Ising SOC in BLG can be precisely quantified, essential for developing theoretical understanding; (ii) the induced SOC is much less sensitive to twist-angle variations compared to moiré systems, allowing for fine control of SOC; and (iii) the proximity to WSe₂ does not induce additional disorder, making experimental insights highly reproducible. We investigated a series of BLG-WSe₂ devices (Fig. 1b) fabricated from the same BLG and WSe₂ crystals, separating the large BLG flake into multiple pieces by atomic-force-microscope-actuated cutting²⁴. With the first BLG piece roughly lattice-aligned with WSe₂ ($\theta \approx 0^\circ$), the following ones are sequentially twisted relative to WSe₂ with a $\sim 6^\circ$ increment (see Methods and Extended Data Fig. 1 for device fabrication details).

To characterize the SOC in our devices, we first perform high-resolution measurements of Shubnikov–de Haas oscillations (Fig. 1f,g) in regions of the n - D phase diagram (n is the doping density, D is the electrical displacement field) that are well-described by non-interacting theory. When a positive D field $D/\epsilon_0 = 0.2$ V/nm is applied, the hole-carrier wavefunctions are strongly polarized towards the top graphene layer adjacent to WSe₂, which in turn induces Ising SOC in BLG^{14,17-19,25,26}. For this D field, Ising SOC is already maximal, i.e., larger D values do not further increase the Ising SOC strength (see Methods and Extended Data Fig. 2 for further discussion). In this regime, we observe a clear beating pattern in longitudinal resistance R_{xx} as a function of out-of-plane magnetic field (B_\perp) at higher doping densities (Fig. 1f), indicating two close oscillation frequencies originating from Fermi pockets of slightly different sizes. To quantitatively

analyze this Fermi-surface imbalance, we normalize the oscillation frequencies of $R_{xx}(1/B_{\perp})$ to the Luttinger volume corresponding to the total doping density. The resulting normalized frequency f_{ν} reveals the fraction of the total Fermi surface area enclosed by a cyclotron orbit. Figure 1h,i shows an example comparison of the density-dependent frequencies f_{ν} from two devices with twist angles $\theta \approx 0^{\circ}$ and 30° , respectively. In both cases, two frequencies ($f_{\nu}^{(1)}$ and $f_{\nu}^{(2)}$) are found satisfying $f_{\nu}^{(1)} + f_{\nu}^{(2)} = 1/2$. These frequencies can be understood as a splitting from $f_{\nu} = 1/4$, which signals the broken four-fold spin-valley symmetry, and are a direct measure of how the Ising SOC modifies the single-particle band structure (Fig. 1c,d). Due to Ising SOC, nominally four-fold degenerate bands separate into two pairs of spin-valley locked bands with slightly different Fermi-surface areas (illustrated in insets of Fig. 1h,i).

We can now confirm experimentally that the induced Ising SOC is modulated by the twist angle θ between WSe₂ and BLG. This is evident from the more pronounced splitting shown in Fig. 1h compared to the one in Fig. 1i. By extracting the sizes of the Fermi pockets corresponding to spin-valley locked bands (see Methods and Extended Data Fig. 2) and comparing them to band-structure calculations, we precisely quantify the Ising SOC strength ($|\lambda_I| \approx 1.6$ meV in Fig. 1h and $|\lambda_I| \approx 0.4$ meV in Fig. 1i, respectively). Fig. 1e summarizes systematic measurements across three sets of moiréless twisting BLG-WSe₂ devices (D1-D3), all of which demonstrate robust θ -modulated Ising SOC strengths. Our results are consistent with the picture that virtual interlayer tunneling is responsible for the induced SOC. When the lattices of BLG and WSe₂ are angle-aligned, i.e., $\theta \approx 0^{\circ}$, the K/K' valleys of BLG couple more effectively to one of the two valleys of WSe₂ (left schematic in Fig. 1e), resulting in a large induced Ising SOC. In contrast, for $\theta \approx 30^{\circ}$, the inter-valley and intra-valley tunneling between WSe₂ and BLG have the same amplitude due to reflection symmetry (right schematic in Fig. 1e). The induced Ising SOC in BLG vanishes accordingly²⁷. The overall twist-angle dependence and the magnitude of Ising SOC are qualitatively consistent with predictions^{16,20–23}.

Using the exquisite twist-angle control of the Ising SOC strength, we explore the SOC-dependent correlated phase diagrams occurring at large D fields. Devices with various Ising strengths all show characteristic R_{xx} features that are associated with strong correlations and superconductivity stabilized at zero magnetic field^{17–19} (Fig. 2a-d, see Extended Data Fig. 3 for all six n - D phase diagrams). Importantly, the main superconducting pocket, which emerges from a polarized state with a dominant population of two out of the four spin-valley flavors^{17,18}, shows a strong dependence on the Ising SOC strength. For low Ising SOC ($|\lambda_I| \approx 0.4$ meV; Fig. 2a), the superconducting region occupies a large D field range, starting from $D/\epsilon_0 \approx 0.3$ V/nm and extending up to $D/\epsilon_0 \approx 1.25$ V/nm. For large Ising SOC ($|\lambda_I| \approx 1.5$ meV; Fig. 2d), however, superconductivity onsets only at $D/\epsilon_0 \approx 0.9$ V/nm. Overall, the value D_{onset} marking the onset of the superconducting pocket grows with increasing $|\lambda_I|$ (Fig. 2j).

This trend of D_{onset} can be understood as a consequence of *interband* interactions between the majority ($K \uparrow, K' \downarrow$) and the minority ($K \downarrow, K' \uparrow$) spin-valley flavors. The difference in hole populations between the majority and minority bands scales with $|\lambda_I|$ and is further enhanced

by Coulomb interactions. Consequently, the region in the phase diagram where both bands have a large density of states (DOS) near the Fermi level is pushed towards higher values of D and n as Ising SOC is increased. The experimentally observed trend is well reproduced by a simple model that takes into account the pairing between majority and minority bands. We perform multiband-superconductivity calculations with polarized normal state and find that the residual Cooper-channel repulsion^{28,29} (v_{TAM}^*) grows with increasing $|\lambda_I|$ and decreases at higher D fields (see Fig. 2l and Supplementary Information (SI), section 1 to 3). The majority-minority interactions that scatter electron pairs between the pair of bands, greatly enhance the screening of the bare repulsion compared to the single-band case. A larger density imbalance between the bands effectively suppresses this interaction, shifting D_{onset} to higher values. Note that the significant role of interband interactions in BLG-WSe₂ is in stark contrast to the case of moiré graphene^{3,30–34}, where superconductivity emerges from a polarized phase in the absence of majority and minority carriers.

Intriguingly, the superconducting critical temperature T_c also shows a striking dependence on $|\lambda_I|$. While D_{onset} is smaller and superconductivity persists over a wide range of D fields for small Ising SOC, the superconducting critical temperature remains low throughout and saturates at $T_c \approx 150$ mK (Fig. 2f,g). In contrast, for large Ising SOC, superconductivity onsets only at higher D fields, but T_c quickly increases, reaching $T_c \approx 500$ mK at the optimal D (Fig. 2h,i). This is the highest T_c reported for crystalline (untwisted) graphene systems. Thus, the optimal critical temperature also shows an increasing trend with $|\lambda_I|$ (Fig. 2k). A detailed three-dimensional map of the optimal critical temperature T_c^{optimal} versus D field and $|\lambda_I|$ extracted from multiple devices is plotted in Fig. 2e. These observations motivate further investigations of the phase diagram with even stronger Ising SOC, e.g., through proximity to other transition metal dichalcogenides or the application of pressure^{35,36}.

The case for investigating devices with large Ising SOC is further emphasized by the observation of two additional superconducting pockets in this regime ($1.4 \text{ meV} \lesssim |\lambda_I| \lesssim 1.6 \text{ meV}$; see Fig. 3a, Fig. 2c,d, and Extended Data Fig. 3). We refer to the observed superconducting regions as SC₁, SC₂, and SC₃, enumerated from higher to lower hole doping, respectively (with the main superconducting region discussed above being SC₂; see Extended Data Fig. 4 for additional temperature and B_{\perp} characterizations). Each superconducting pocket descends from a distinct flavor-symmetry-breaking normal state (Fig. 3b-f) and is terminated by a first-order symmetry-breaking phase transition (marked by black dashed lines in Fig. 3b-f) on the low-doping side. Region SC₁ features an optimal critical temperature $T_c \approx 60$ mK (Fig. 3b inset), while the critical temperatures for SC₂ and SC₃ are $T_c \approx 500$ mK and 100 mK, respectively (Fig. 3d). The normal state of SC₁ is the only one that can be directly related to the non-interacting band structure. Quantum oscillations in this regime ($-9 \lesssim n \lesssim -7.6 \times 10^{11} \text{ cm}^{-2}$, Fig. 3c) show two main frequencies (marked by blue and orange arrows) obeying $2 \cdot f_{\nu}^{(1)} + 6 \cdot f_{\nu}^{(2)} \approx 1$. This indicates two large Fermi pockets from the two majority Ising flavors and six small pockets originating from trigonal warping³⁷ of the two minority Ising flavors¹⁸ (Fig. 3c left schematic); we denote the flavor-polarized phase as FP(2, 6) (FP(n, m) denotes a flavor-polarized phase with n and m degenerate-sized Fermi pockets, from large to small).

Ultrahigh-resolution quantum oscillations reveal the unusual features of the Fermi surfaces in the correlated normal states forming SC₂ and SC₃. In the higher-doping region of SC₂ ($n \lesssim -8.25 \times 10^{11} \text{ cm}^{-2}$, Fig. 3e), we observe two dominant oscillation frequencies marked by blue ($f_\nu^{(1)}$) and orange ($f_\nu^{(2)}$) lines in Fig. 3f, satisfying $2 \cdot f_\nu^{(1)} + 4 \cdot f_\nu^{(2)} \approx 1$ (black line). Thus, the normal state, denoted as FP(2, 4), is a flavor-polarized phase hosting two majority and four minority Fermi pockets. The occupation of two out of the three trigonal-warping pockets for both the minority spin-valley flavors implies a nematic normal state that breaks the C_3 rotational symmetry¹⁸ (Fig. 3f left schematic). Remarkably, we observe a different Fermi-pocket configuration in the doping range $-8.25 \lesssim n \lesssim -7.1 \times 10^{11} \text{ cm}^{-2}$ within the same superconducting pocket. Here, the lowest third frequency $f_\nu^{(3)}$ (green line in Fig. 3f) can be clearly resolved (see Methods and Extended Data Fig. 5 to 7 for frequency extraction). Starting from the same value as $f_\nu^{(2)}$, the value of $f_\nu^{(3)}$ rapidly decreases to zero at the low-doping phase boundary, implying that two out of the four small Fermi pockets shrink considerably in this density range. We denote this phase as FP(2, 2, 2) in view of the relation $2 \cdot f_\nu^{(1)} + 2 \cdot f_\nu^{(2)} + 2 \cdot f_\nu^{(3)} \approx 1$. Here, the second and third numbers (2 and 2) imply an additional broken symmetry within the trigonal-warping pockets^{38,39} (orange and green pockets of the middle schematic in Fig. 3f), signaling a nematic redistribution of holes. This remarkable continuous transition from FP(2, 2, 2) to FP(2, 4) within the superconducting dome has a significant impact on the in-plane magnetic field response of SC₂ (see Fig. 4 and the associated discussion).

A rather exceptional correlated phase denoted FP(1, 3, 1) emerges upon further decreasing the doping ($-7.1 \lesssim n \lesssim -5.7 \times 10^{11} \text{ cm}^{-2}$; Fig. 3e,f). The Fermi-surface configuration is reflected in three oscillation frequencies obeying $f_\nu^{(4)} + 3 \cdot f_\nu^{(5)} + f_\nu^{(6)} \approx 1$, with $f_\nu^{(4)}$ being larger than 1/2, ensuring that the largest Fermi pocket is non-degenerate (see Methods and Extended Data Fig. 8 to 10 for further discussion). Remarkably, this normal state supports the superconducting region SC₃, although all Fermi pockets have odd multiplicities. The combination of superconductivity and odd Fermi-pocket multiplicities strongly points at an inter-valley coherent (IVC) state⁴⁰⁻⁴⁶ (purple schematic of Fig. 3f). This is further corroborated by an analysis of the response of the phase boundaries to a B_\perp field⁴² (see Methods and Extended Data Fig. 11). The odd multiplicity of all Fermi pockets excludes the possibility of conventional s -wave pairing, suggesting unconventional superconductivity. Moreover, provided that the pockets are intrinsically superconducting, the number of three mid-size Fermi pockets ($f_\nu^{(5)}$) implies time-reversal symmetry breaking regardless of the inter-valley coherent nature^{44,47-49}. It is interesting that SC₃ only develops in a multi-band situation and not from one of the IVC-ordered normal states at lower hole doping with a single or a smaller number of Fermi pockets (see Extended Data Fig. 11).

All three superconducting pockets show extraordinary resilience to in-plane magnetic field B_\parallel . SC₁ is characterized by an in-plane critical field $B_{c\parallel} \approx 2.5 \text{ T}$, significantly higher than observed previously¹⁸ (Extended Data Fig. 12). SC₂ and SC₃ show distinct features in the B_\parallel response, reflecting the highly unusual intertwining with the underlying normal states. Fig. 4a,b shows the dependence of R_{xx} on in-plane magnetic field B_\parallel (Fig. 4a) and temperature (Fig. 4b) measured

at $D/\epsilon_0 \approx 1.265$ V/nm. SC_2 occupies a significantly larger doping range, and its optimal T_c is roughly five times that of SC_3 (Fig. 4b). In comparison, the two superconducting regions show a striking response to B_{\parallel} . While SC_2 is fully suppressed by $B_{\parallel} \approx 3$ T, SC_3 persists up to $B_{\parallel} = 7$ T (Fig. 4a) at the phase boundary. Crucially, the optimal critical temperature T_c^{optimal} of SC_3 appears to be insensitive to B_{\parallel} (Fig. 4e and Extended Data Fig. 13), with the superconducting domes at $B_{\parallel} = 0$ T and $B_{\parallel} = 3$ T being almost the same (Fig. 4c,d). For a weak-coupling spin-singlet Bardeen–Cooper–Schrieffer (BCS) superconductor, the Pauli limit B_p is related to the zero-magnetic-field critical temperature $T_c(0)$ as $B_p = 1.86 \text{ T/K} \times T_c(0)$. $T_c(0) = 100$ mK for SC_3 would produce a Pauli limit $B_p = 0.186$ T. Thus, the observed in-plane critical field $B_{c\parallel} = 7$ T yields a Pauli-limit violation ratio (PVR) $B_{c\parallel}/B_p \sim 40$, placing SC_3 among the superconducting phases with the highest Pauli-limit violation ratios⁴⁻⁷. Note that the exceedingly large PVR is not present in the other two superconducting regions where Fermi pockets of the same size appear in pairs, further reflecting the remarkable nature of SC_3 .

While having a significantly lower PVR, the analysis of SC_2 provides further insights into the pairing scenarios. SC_2 features two doping regions with distinct B_{\parallel} responses (Fig. 4f,g) that are directly intertwined with the continuous transition from FP(2, 2, 2) to FP(2, 4) (Fig. 4h,i). Figure 4f,g shows representative R_{xx} versus temperature and B_{\parallel} measured in the overdoped and underdoped regions ($n = -8.5$ and $-6.9 \times 10^{11} \text{ cm}^{-2}$, respectively) for $D/\epsilon_0 = 1.2$ V/nm. SC_2 exhibits the same $T_c(0) \approx 200$ mK at both doping densities, but the B_{\parallel} responses are distinct. The overdoped T_c is quickly suppressed by B_{\parallel} following a conventional quadratic scaling (Fig. 4f). The underdoped T_c , however, is insensitive to B_{\parallel} for $B_{\parallel} \leq 1$ T (Fig. 4g), with the depairing at higher fields $B_{\parallel} > 1.5$ T likely due to the Fermi-surface changes induced by B_{\parallel} .

To quantify the B_{\parallel} -induced suppression of SC_2 , we fit T_c versus B_{\parallel} by $T_c(B_{\parallel}) = T_c(0) - \alpha \cdot B_{\parallel}^2$, where α quantifies the pair-breaking tendency of B_{\parallel} . The resulting α shows a striking dependence on doping (Fig. 4h). At higher doping, α plateaus around 0.08 K/T^2 . At lower doping, α approaches zero, indicating vanishing sensitivity to B_{\parallel} . Importantly, the qualitative change in α (Fig. 4h) coincides with the redistribution of the trigonal-warping pockets (Fig. 4i). The region with the plateau ($-8.8 \lesssim n \lesssim -7.3 \times 10^{11} \text{ cm}^{-2}$) and the region with the rapidly changing α ($-7.3 \lesssim n \lesssim -6.6 \times 10^{11} \text{ cm}^{-2}$) correspond to the FP(2, 4) and FP(2, 2, 2) phases, respectively. Within the FP(2, 2, 2), both the value of α and the size of the smallest Fermi pockets (green pockets of the schematics in Fig. 4h) approach zero at the phase boundary ($n \approx -6.6 \times 10^{11} \text{ cm}^{-2}$). These observations suggest that the smallest Fermi pockets determine the B_{\parallel} response (see Extended Data Fig. 14 to 16 for additional data).

The disparity in the response of the two SC_2 regions to B_{\parallel} invites an analysis of possible microscopic mechanisms. We propose that this disparity may be attributed to the prominence of majority-minority interband interactions, so that the B_{\parallel} response (Fig. 4f-i) and the trend observed in D_{onset} (Fig. 2j) share a common origin. Due to strong interactions, a modest B_{\parallel} (compared to $|\lambda_I|$) may lead to significant spin canting, where majority- (minority-) band spins cant towards (away from) the magnetic field direction (see SI, section 5). In the spin-canted normal state^{44,50}, the

interband (intra-band) Cooper-channel interactions are naturally suppressed (enhanced) due to the in-plane spin projection of the scattered Copper pairs. As a consequence, since interband scattering is beneficial to pairing, one expects an appreciable decrease in T_c with applied B_{\parallel} (Fig. 4j,l). On the other hand, further symmetry breaking in the minority bands (e.g., spin or valley polarization) may critically suppress pairing between minority carriers and thus decouple them completely from the majority band in the Cooper channel. In such a scenario provided that the minority bands of FP(2, 2, 2) are valley-polarized (right schematic in Fig. 4k), one expects the adverse magnetic field effects on the interband interaction to gradually disappear, making the superconductor less field-sensitive (Fig. 4k,m). This coincides with the experimental trend in Fig. 4f-i. Note that the same interband B_{\parallel} -suppression mechanism is consistent with the hierarchy of PVR between SC₁, SC₂, and SC₃ (SI, section 5). Our conclusions are further supported by an analysis of conventional depairing mechanisms within the Ising superconductor framework^{17,51–53}, which is qualitatively inconsistent with the experimental observations (see Methods and SI, section 6).

Unprecedented control over the strength of Ising SOC in BLG allowed us to explore its rich set of superconducting regions systematically. Superconductivity occurs for a diverse set of Fermi-pocket configurations, including for Fermi pockets with odd multiplicity pointing at unconventional superconductivity. Remarkably, all the superconductors exhibit distinctive resilience to in-plane magnetic field. A newly discovered inter-valley coherent Fermi-pocket configuration exhibits a PVR value, which reaches one of the highest values for any superconductor to date. All the superconducting regions are multiband superconductors, which we argue to explain differences in their resilience to in-plane fields and their dependence on the displacement field. More generally, the approach of inducing tunable symmetry-breaking fields via moiréless-twist engineering, can be applied to a broad family of van der Waals materials and extended beyond SOC to include magnetism, charge orders, etc. This opens promising avenues towards tailoring desired perturbations and realizing exotic phases of matter on demand.

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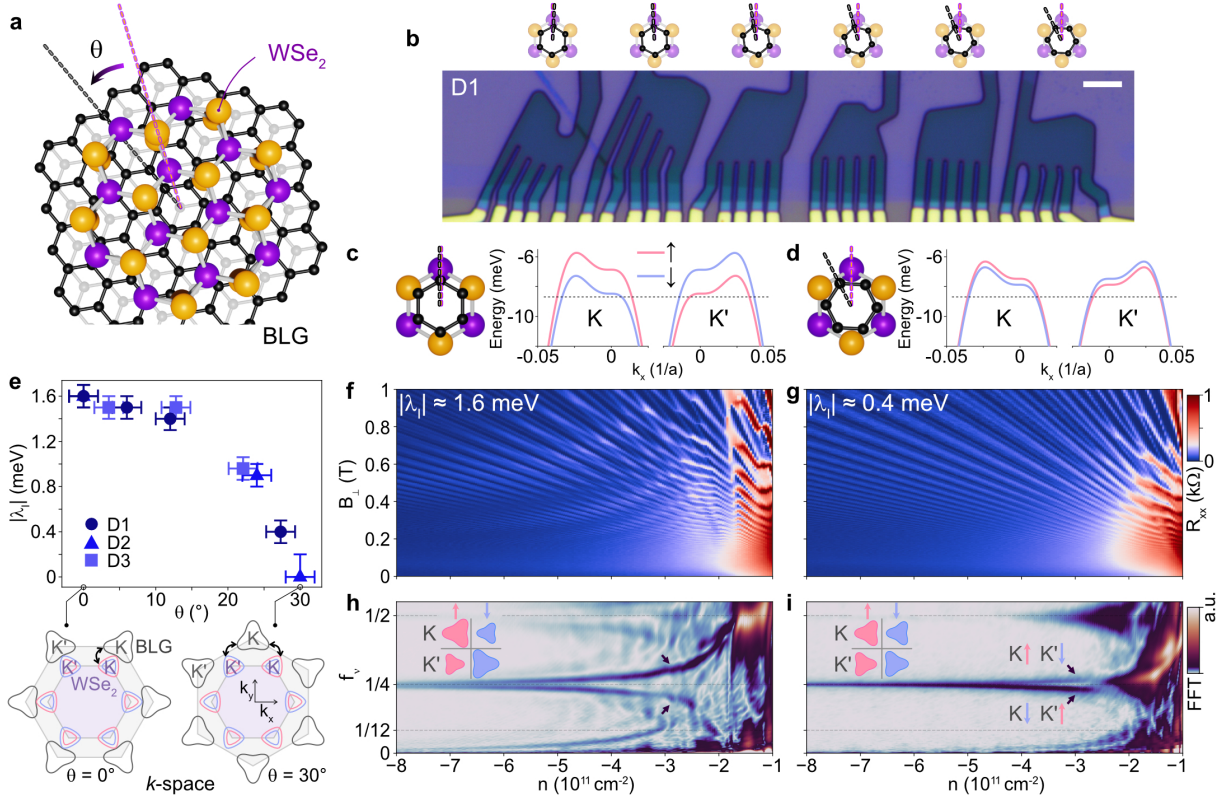


Figure 1 | Programmable Ising SOC by interfacial twisting between BLG and WSe₂. **a**, Schematic showing the twisting of the BLG-WSe₂ interface; tuning the interfacial twist angle θ between the two largely lattice-mismatched materials modifies the Ising SOC strength $|\lambda_I|$ and the correlated phase diagram. **b**, Optical image of the device set D1. Crystal axes of graphene and WSe₂ are rotated relative to each other with an angle $\theta \sim 0^\circ, 6^\circ, 12^\circ, 18^\circ, 24^\circ,$ and 30° for the six devices, respectively. The scale bar corresponds to $5\mu\text{m}$. **c,d**, Non-interacting valence bands of BLG near the K and K' points of the Brillouin zone at $D/\epsilon_0 = 0.2$ V/nm, with proximitized Ising SOC $|\lambda_I| \approx 1.6$ meV (**c**) and 0.4 meV (**d**), respectively. **e**, Ising SOC strength $|\lambda_I|$ versus BLG-WSe₂ interfacial twist angle θ ; data were extracted from three sets of devices D1-D3. The bottom schematics show the relative rotation between the BLG and WSe₂ Brillouin zones. At $\theta \approx 0^\circ$, K/K' valleys of BLG couple more effectively to one of the two WSe₂ valleys, resulting in large induced Ising SOC. In contrast, at $\theta \approx 30^\circ$, inter-valley and intra-valley tunneling between WSe₂ and BLG have the same amplitude by reflection symmetry so that Ising couplings of opposite sign cancel each other and result in vanishing proximity value. **f,g**, R_{xx} versus out-of-plane magnetic field B_\perp and doping n measured at $D/\epsilon_0 = 0.2$ V/nm for devices with $|\lambda_I| \approx 1.6$ meV (**f**) and 0.4 meV (**g**), respectively. **h,i**, Fast Fourier transform (FFT) of $R_{xx}(1/B_\perp)$ versus n and f_ν , where f_ν denotes the quantum oscillation frequency normalized to the Luttinger volume. The arrow-marked FFT splittings reflect the Ising-induced Fermi-surface imbalance within each valley, where larger Ising SOC (**h**) features a larger splitting than small Ising SOC (**i**).

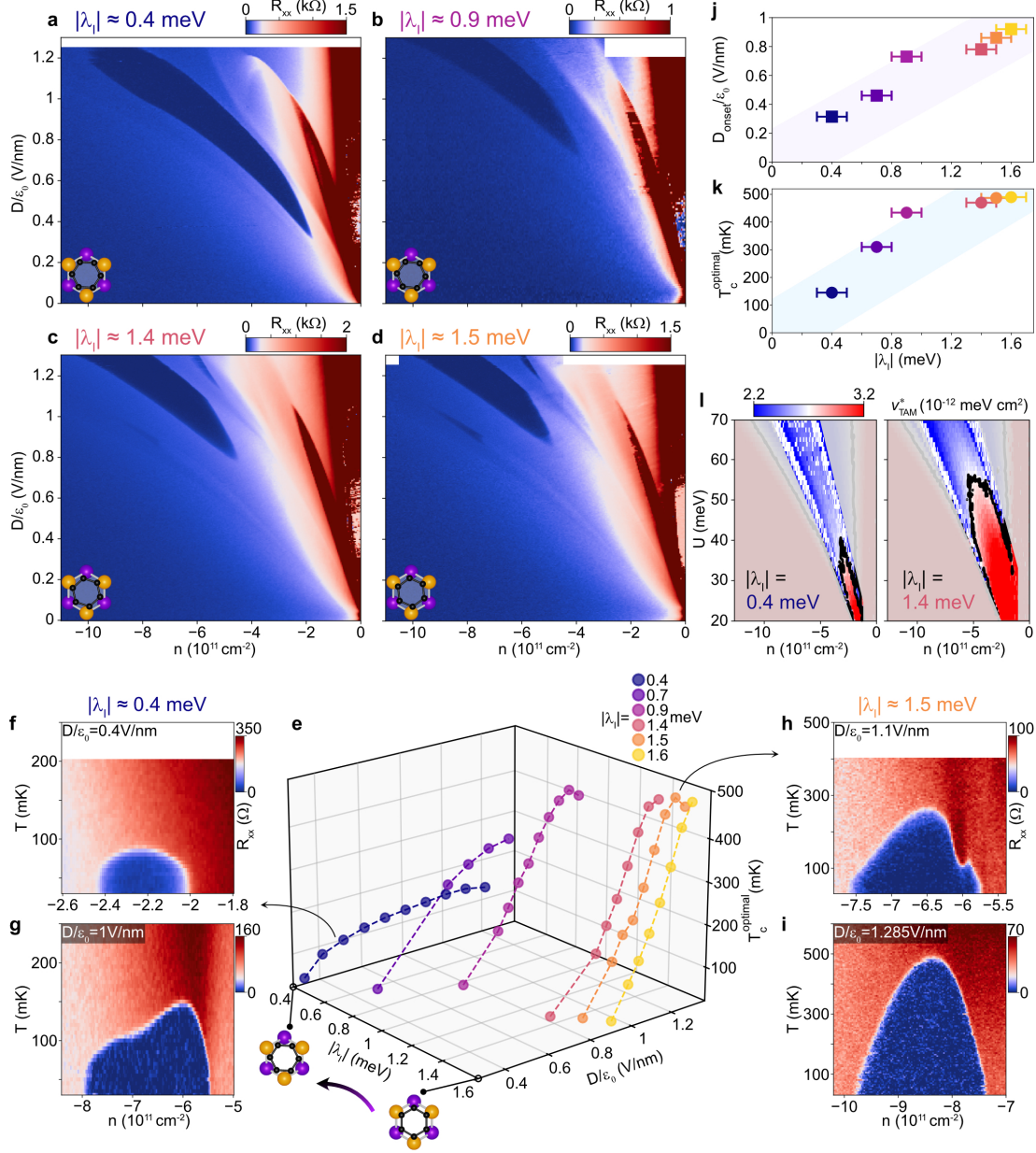


Figure 2 | Twist-programmable superconducting phase diagram. **a–d**, R_{xx} versus doping density n and displacement field D for devices with Ising strength $|\lambda_I| \approx 0.4$ meV (**a**), 0.9 meV (**b**), 1.4 meV (**c**), and 1.5 meV (**d**), respectively. **e**, Optimal superconducting critical temperature T_c^{optimal} versus $|\lambda_I|$ and D . **f,g**, R_{xx} versus doping n and temperature for a device with $|\lambda_I| \approx 0.4$ meV, showing superconducting domes at $D/\epsilon_0 = 0.4$ V/nm (**f**) and 1 V/nm (**g**), respectively. **h,i**, R_{xx} versus doping n and temperature for a device with $|\lambda_I| \approx 1.5$ meV, showing superconducting domes at $D/\epsilon_0 = 1.1$ V/nm (**h**) and 1.285 V/nm (**i**), respectively. **j,k**, Displacement field $D_{\text{onset}}/\epsilon_0$ at which superconductivity onsets (**j**) and optimal critical temperature T_c^{optimal} (**k**) versus Ising SOC strength $|\lambda_I|$. **l**, The residual Cooper channel repulsion v_{TAM}^* versus doping n and interlayer potential difference U for $|\lambda_I| = 0.4$ meV (left) and 1.4 meV (right), respectively.

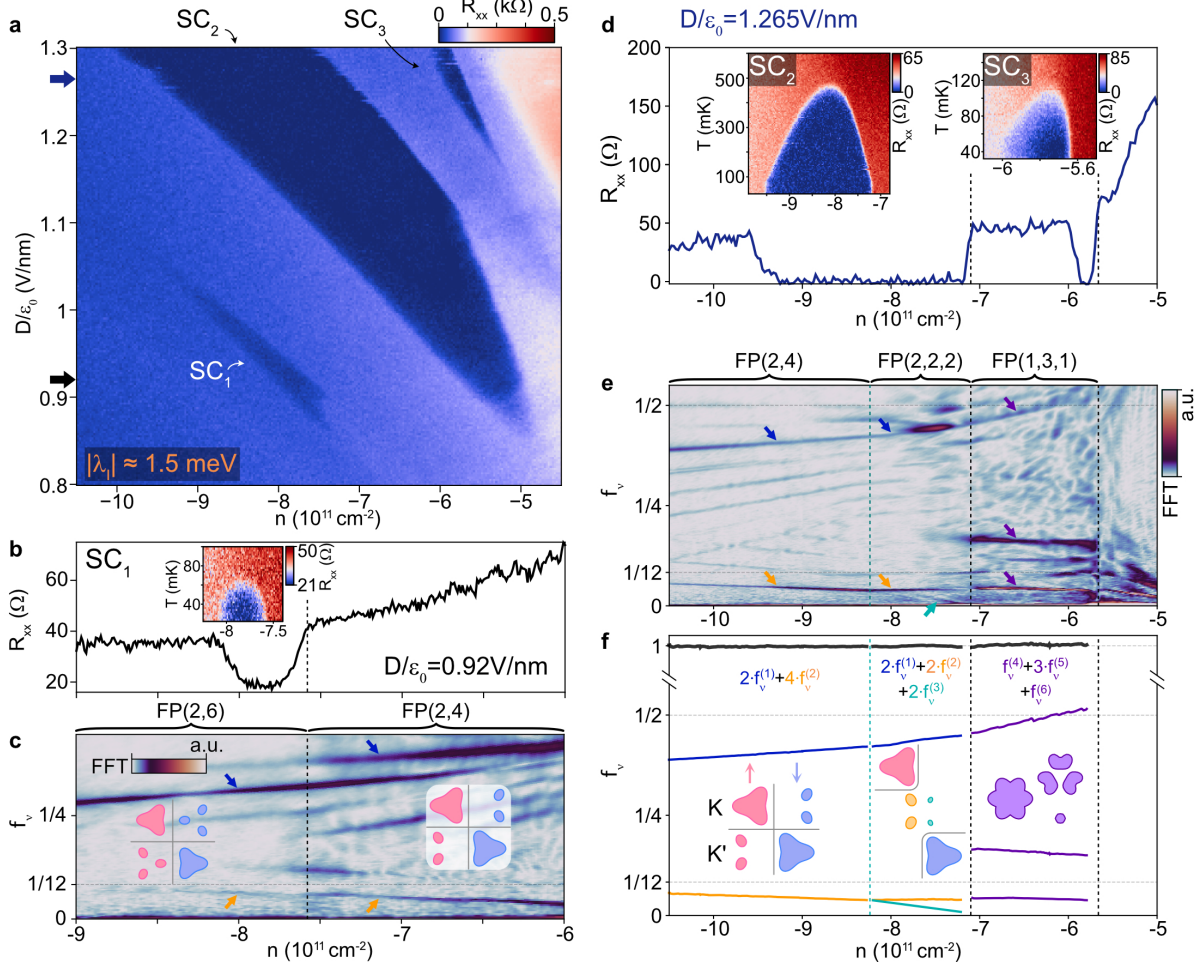


Figure 3 | Superconductivity across nematic redistribution and from inter-valley coherence. **a**, R_{xx} versus doping density n and displacement field D for a device with Ising SOC strength $|\lambda_I| \approx 1.5$ meV, focusing around the phase space where the three superconducting regions coexist. **b**, R_{xx} versus n measured at $D/\epsilon_0 = 0.92$ V/nm. The inset shows R_{xx} versus n and temperature for the superconducting dome SC_1 . **c**, Frequency-normalized FFT of $R_{xx}(1/B_\perp)$ over the same doping range as in **b**; schematics show the corresponding flavor symmetry-breaking Fermi surfaces. **d**, R_{xx} versus n measured at $D/\epsilon_0 = 1.265$ V/nm. Insets show R_{xx} versus n and temperature for the superconducting domes SC_2 (left) and SC_3 (right), respectively. **e**, Frequency-normalized FFT of $R_{xx}(1/B_\perp)$ over the same doping range as in **d**. The arrows mark the primary FFT peaks, as shown in **f**. The green dashed line marks the continuous transition from FP(2, 2, 2) to FP(2, 4); black dashed lines mark first-order flavor symmetry-breaking transitions. **f**, Intensity peaks in f_ν extracted from **e**. The black solid lines around $f_\nu = 1$ indicate the results from the Luttinger sum rule. Schematics show the possible flavor-polarized phases, from left to right corresponding to spin-valley locked nematic FP(2, 4), nematic FP(2, 2, 2) with two sizes (green and orange) of trigonal-warping pockets, and inter-valley coherent FP(1, 3, 1).

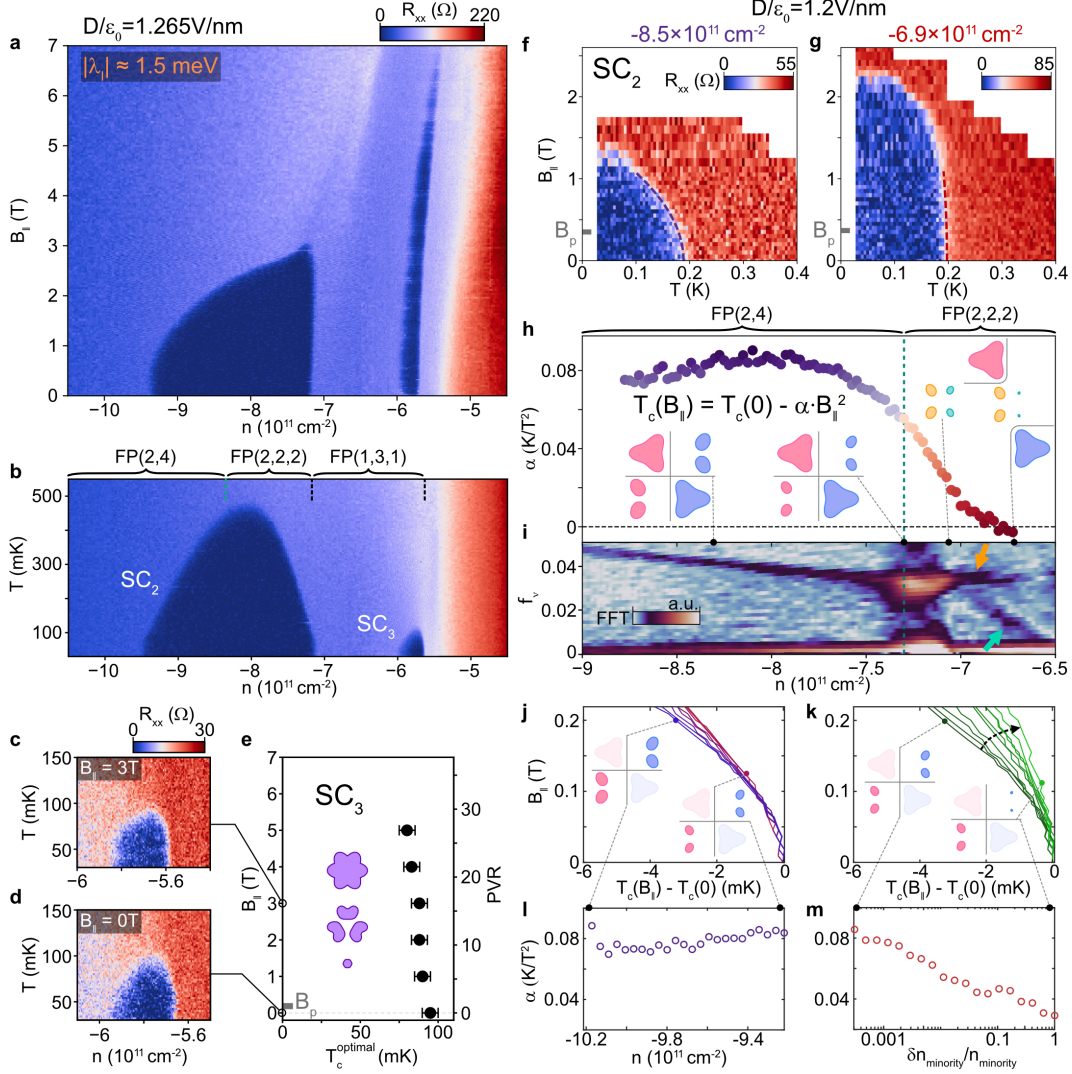


Figure 4 | Ultra-high Pauli-limit violation and nematicity-intertwined B_{\parallel} depairing. **a**, R_{xx} versus doping n and in-plane magnetic field B_{\parallel} at $D/\epsilon_0 = 1.265$ V/nm for a device with $|\lambda_I| \approx 1.5$ meV. **b**, R_{xx} versus n and temperature at the same D . **c,d**, R_{xx} versus n and temperature for SC_3 measured at $B_{\parallel} = 0$ T (**c**) and 3 T (**d**), respectively. **e**, Optimal critical temperature T_c^{optimal} of SC_3 versus B_{\parallel} . The grey bar marks the Pauli limit B_p . **f,g**, R_{xx} versus temperature and B_{\parallel} at $n = -8.5 \times 10^{11} \text{ cm}^{-2}$ (**f**) and $-6.9 \times 10^{11} \text{ cm}^{-2}$ (**g**), respectively for $D/\epsilon_0 = 1.2$ V/nm. The colored dashed lines are quadratic fitting by $T_c(B_{\parallel}) = T_c(0) - \alpha \times B_{\parallel}^2$. **h**, Coefficient α versus doping n within the SC_2 dome at $D/\epsilon_0 = 1.2$ V/nm. **i**, Normalized FFT of $R_{xx}(1/B_{\perp})$ over the same n and D range as in **h**, focusing at low frequencies. Green dashed line marks the nematic redistribution of holes from FP(2,4) to FP(2,2,2). Schematics in **h** show the Fermi-surface evolution versus n , where the smallest trigonal-warping pockets (green) grow rapidly from low to high doping ($-7.3 \lesssim n \lesssim -6.6 \times 10^{11} \text{ cm}^{-2}$). **j,k**, Theoretical B_{\parallel} depairing with the prominent interband pairing (**j**) and the suppressed case by valley polarization (**k**). **l,m**, Theoretical α versus n for FP(2,4) (**l**) and versus minority imbalance $\delta n_{\text{minority}}/n_{\text{minority}}$ for FP(2,2,2) (**m**).

Methods

Device fabrication: The majority of the fabrication processes follow the standard flake transfer and lithography explained in a previous study¹⁷. Here, we focus on the interfacial twisting between BLG and WSe₂. Large flakes of BLG and WSe₂ are exfoliated on SiO₂/Si chips. The crystal orientation of WSe₂ can be identified by second harmonic generation⁵⁴ (SHG; Extended Data Fig. 1b), where the polarization of the incident and reflected beams are selected to lie parallel to the scattering plane. The directions with maximized SHG signal correspond to the in-plane crystal orientations along the W-Se direction (armchair direction). BLG is somewhat trickier. We identify flakes with long straight edges forming angles that are multiple of 30°, e.g., three edges form two angles of 150° in Extended Data Fig. 1c. The configuration is consistent with the assignment that the straight edges are along the zigzag- or armchair-edge direction of graphene. We then cut the large BLG flake into small pieces²⁴; Extended Data Fig. 1d. First, pick up topmost hBN, top graphite gate, top hBN dielectric, and the large WSe₂ flake using propylene carbonate (PC) film on a polydimethylsiloxane (PDMS). Then, align the straight edge of BLG with the crystal orientation of WSe₂ and control the approach of PC/PDMS stamp so that only one BLG piece is picked up. SiO₂/Si chip was manually rotated by an angle $\theta \sim 6^\circ$, and a second piece of BLG was picked up but not overlapping with the first one. Repeat the same processes for the remaining BLG pieces (Extended Data Fig. 1f,g). Depending on whether the BLG straight edge used for alignment is along the zigzag or armchair direction, the crystal axes of the six BLG pieces are rotated relative to the WSe₂ axis by an angle $\theta \sim 0^\circ, 6^\circ, 12^\circ, 18^\circ, 24^\circ, \text{ and } 30^\circ$ (armchair direction), or vice versa (zigzag direction). The two configurations can be distinguished by measuring the Ising SOC strengths of the devices at the two ends. The large (small) Ising device corresponds to $\sim 0^\circ$ ($\sim 30^\circ$) alignment due to the reflection symmetry^{16,20-22}. A typical finished stack is shown in Extended Data Fig. 1h; a series of different rotation angles between BLG and WSe₂ can be clearly seen from the optical image. The stack went through standard lithographic and etching processes for final device preparation (Extended Data Fig. 1i).

Measurements: All measurements were performed in a dilution refrigerator (Oxford Triton) with a base temperature of ~ 30 mK and an 1T/1T/9T (XYZ) superconducting vector magnet, using standard low-frequency lock-in amplifier techniques. Unless otherwise specified, measurements are taken at the base temperature. Frequencies of the lock-in amplifiers (Stanford Research, models 865a) were kept in the range of 7 – 40 Hz in order to reduce the electronic noise and measure the device’s DC properties. The AC excitation was kept < 5 nA; most measurements were taken at 1 nA to preserve the linearity of the system and to avoid disturbing the fragile states at low temperatures. Each of the DC fridge lines passes through cold filters, including 4 Pi filters that filter out a range from ~ 80 MHz to > 10 GHz, as well as a two-pole RC low-pass filter.

Ising SOC: One way to quantify the WSe₂-induced Ising SOC $H_I = \frac{1}{2}\lambda_I\tau_zs_z$ (λ_I is the Ising SOC strength in the main text) is to probe the octet zeroth Landau level (LL) in BLG. Note that these LL energies are not sensitive to Rashba SOC¹³. The sets of two Landau levels that cross at filling factors $\nu = \pm 3$ have opposite layer polarizations, so that their energy difference (at zero D

field) is given by $\Delta E = E_Z \pm \lambda_I/2$ (E_Z is the Zeeman gap between spin-up and spin-down LLs). Therefore, the critical field B_\perp^* that makes ΔE vanish is $2E_Z = 2g\mu_B B_\perp^* = \lambda_I$. However, this method doesn't work when λ_I is negative since the energy-level crossing is not inverted¹⁵.

Independently, $|\lambda_I|$ can also be extracted from the doping-dependent FFT splitting of the quantum oscillations, regardless the sign of λ_I (Fig. 1f-i and Extended Data Fig. 2a). Extended Data Fig. 2b,c shows the doping-dependent FFT splitting B_{split} measured at different D fields within the non-interacting phase (schematics in Fig. 1h,i). Ising-type splitting is suppressed with increasing $|n|$, in contrast to the Rashba-type splitting which increases with increasing $|n|$ ¹⁷. The detailed mapping of B_{split} as a function of n and D enables comparison to single-particle band structure calculation that quantifies Ising-induced Fermi surface imbalance. The dashed lines in Extended Data Fig. 2b,c are calculated frequency splittings for $|\lambda_I| \approx 1.4$ meV (Extended Data Fig. 2b) and $|\lambda_I| \approx 0.4$ meV (Extended Data Fig. 2c), respectively. Both cases roughly match the experimental data. The overall trend is that (i) at constant $|\lambda_I|$, higher D features larger B_{split} and (ii) at constant D , higher $|\lambda_I|$ features larger B_{split} . The observed trends put strong constraints on the estimates of the Ising SOC strength. Note that one single Ising SOC strength provides a good fit to the data at different D fields (from $D/\epsilon_0 = 0.2$ V/nm to 1 V/nm; Extended Data Fig. 2b), suggesting that Ising SOC is already maximal at $D/\epsilon_0 = 0.2$ V/nm and larger D values do not further increase the Ising SOC strength.

Identification of FP(2, 2, 2) phase: Ultrahigh-resolution quantum oscillations at high D fields allow for resolving subtle symmetry-breaking Fermi pockets. Looking carefully at the FFT frequency $f_\nu^{(2)}$ in Extended Data Fig. 5b and Extended Data Fig. 6b,d, $f_\nu^{(2)}$ decreases monotonically with lowering doping until reaching $n \approx -8.25 \times 10^{11} \text{ cm}^{-2}$ for $D/\epsilon_0 = 1.265$ V/nm ($n \approx -7.2 \times 10^{11} \text{ cm}^{-2}$ for $D/\epsilon_0 = 1.2$ V/nm), beyond which the dependence of $f_\nu^{(2)}$ is flattened while $f_\nu^{(1)}$ keeps increasing throughout. This indicates that the sum rule $2 \cdot f_\nu^{(1)} + 4 \cdot f_\nu^{(2)} \approx 1$ of the FP(2, 4) phase at higher doping is no longer satisfied for lower dopings, suggesting an altered Fermi-surface structure. Indeed, measuring quantum oscillations to higher B_\perp field reveals the emergence of a third very low frequency around the phase boundary as marked by the green arrows in Extended Data Fig. 7. FFT data shown in Extended Data Fig. 5b and Extended Data Fig. 6b,d clearly reveal the third frequency $f_\nu^{(3)}$ growing rapidly from zero at the phase boundary to a value matching $f_\nu^{(2)}$ at slightly higher doping. The frequencies obey $2 \cdot f_\nu^{(1)} + 2 \cdot f_\nu^{(2)} + 2 \cdot f_\nu^{(3)} \approx 1$, as discussed in the main text corresponding to an additional symmetry breaking with trigonally warped pockets of two sizes $f_\nu^{(2)}$ and $f_\nu^{(3)}$.

Identification of FP(1, 3, 1) phase: The identification of FP(1, 3, 1) phase is more subtle, involving extensive quantum oscillation measurements. The raw data (Extended Data Fig. 7a,b; $n \approx -6.6 \times 10^{11} \text{ cm}^{-2}$ to $-5.3 \times 10^{11} \text{ cm}^{-2}$ taken at $D/\epsilon_0 \approx 1.2$ V/nm) reveal three oscillation frequencies. A high frequency marked $f_\nu^{(4)}$ appears clearly. At really low $B_\perp \sim 0.05$ T, a relatively low frequency called $f_\nu^{(6)}$ onsets. Further increasing B_\perp , each $f_\nu^{(6)}$ period splits into four, giving rise to $f_\nu^{(5)}$ which is indeed roughly four times the frequency $f_\nu^{(6)}$ (Extended Data Fig. 7c).

It is natural to ask whether $f_\nu^{(5)}$ is simply a higher (fourth) harmonic of $f_\nu^{(6)}$. This can be answered by the measurements at low D fields in the same phase region (Extended Data Fig. 8 and 9). Frequencies are marked by arrows. When lowering the D fields, $f_\nu^{(4)}$ gradually increases, while $f_\nu^{(5)}$ and $f_\nu^{(6)}$ gradually decrease. At $D/\epsilon_0 = 1$ V/nm (Extended Data Fig. 8b,d,f), $f_\nu^{(5)}$ already deviates from being four times the value of $f_\nu^{(6)}$. Eventually at $D/\epsilon_0 = 0.85$ V/nm (Extended Data Fig. 8a,c,e), the frequency $f_\nu^{(6)}$ completely disappears while $f_\nu^{(5)}$ independently survives. This D evolution of the two frequencies ($f_\nu^{(5)}$ and $f_\nu^{(6)}$) supports their independence. Meanwhile at $D/\epsilon_0 = 0.85$ V/nm, the existing two frequencies ($f_\nu^{(4)}$ and $f_\nu^{(5)}$) obey $f_\nu^{(4)} + 3 \cdot f_\nu^{(5)} \approx 1$; we denote the flavor-polarized phase at this D field as FP(1, 3). The above D -field evolution indicates that the FP(1, 3, 1) phase at high D develops from the FP(1, 3) phase at low D as D is increased.

After establishing the existence of three frequencies, we comment on the number of pockets for each type. This relies on the correct identification of intrinsic Fermi-surface frequencies and their harmonics. At slightly higher B_\perp , magnetic breakdown⁵⁵ kicks in as B_\perp -assisted electron tunneling between different Fermi surfaces. Consequently, the pronounced frequencies might be a sum (or difference) of two base frequencies instead of the intrinsic ones. This is the case for FP(1, 3) and FP(1, 3, 1) phase. Extended Data Fig. 8c shows the normalized FFT from quantum oscillations going up to $B_\perp = 0.45$ T. The frequency peak at $f_\nu \sim 0.75$ is stronger than the one at $f_\nu \sim 0.6$ (marked by the arrow). However, the relative intensity changes by reducing the B_\perp range to 0.23T (Extended Data Fig. 10a). At this condition, the peak at $f_\nu \sim 0.6$ is stronger than the one at $f_\nu \sim 0.75$, suggesting that the one marked by the arrow ($f_\nu \sim 0.6$ in Extended Data Fig. 10a) is the intrinsic frequency; the one at $f_\nu \sim 0.75$ is instead a sum harmonic $f_\nu^{(4)} + f_\nu^{(5)}$. By identifying the intrinsic high frequency $f_\nu^{(4)}$, one obtains $f_\nu^{(4)} + 3 \cdot f_\nu^{(5)} \approx 1$, indicating one large and three small Fermi surfaces, i.e., FP(1, 3). A similar situation holds for the other D fields, such as at $D/\epsilon_0 = 1.2$ V/nm (see Extended Data Fig. 9c and Extended Data Fig. 10c), where we find $f_\nu^{(4)} + 3 \cdot f_\nu^{(5)} + f_\nu^{(6)} \approx 1$.

Inter-valley coherence: The occurrence of superconducting state SC₃ in the symmetry-breaking state FP(1, 3, 1) strongly indicates the inter-valley coherent nature of FP(1, 3, 1). Focusing on the single largest Fermi pocket ($f_\nu^{(4)}$) that is non-degenerate, there are two options: it is either valley-polarized and therefore breaks time-reversal symmetry, or it is inter-valley coherent. Coherence between the K and K' valleys would restore time reversal symmetry for the largest Fermi pocket, naturally more susceptible to pairing. Note that in moiré graphene, it is established that superconductivity originates from an inter-valley-coherent order^{40,41}.

Independent evidence for inter-valley coherence comes from analyzing the evolution of phase boundaries as a function of B_\perp . An out-of-plane magnetic field B_\perp favors valley-polarized states that are characterized by large orbital moments. As B_\perp field is increased, valley-polarized states with large orbital moments are expected to take over more of the phase space compared to valley-balanced states⁴². The evolution of the phase boundaries with B_\perp can be clearly identified from quantum oscillations (Extended Data Fig. 11). Here, the lowest doping density range ($n >$

$-3 \times 10^{11} \text{ cm}^{-2}$) corresponds to a spin-valley locked FP(6) phase¹⁷. Within this phase, the K and K' valleys are equally populated with opposite spins, resulting in zero net orbital moment. At the doping density $-3 > n > -4.3 \times 10^{11} \text{ cm}^{-2}$, the oscillation frequency peaks at $f_\nu = 1$ indicating FP(1) phase. The phase space shows a rich evolution: a phase transition develops with increasing B_\perp , consistent with a spin-valley polarized FP(1) (red line in Extended Data Fig. 11b) emerges when B_\perp is applied. Importantly, at the lowest B_\perp ($B_\perp \sim 0 \text{ T}$), the phase boundary between FP(1) and FP(6) (black dashed line at $n \approx -3 \times 10^{11} \text{ cm}^{-2}$) doesn't move with B_\perp , suggesting that the FP(1) at $B_\perp \sim 0 \text{ T}$ is characterized by coherence between the two valleys (over the spin-valley polarized phase), so that the orbital moments cancel. The same logic applies to the other symmetry-breaking phases at slightly higher doping. A large FFT frequency dominates at $f_\nu > 1/2$ while the phase boundaries persist in doping without moving when B_\perp is applied, suggesting the existence of one large Fermi pocket with diminished or no orbital moments and hence inter-valley coherence for FP(1, 3, 1).

Sample alignment with in-plane magnetic field: In-plane-field measurements were performed by mounting the sample vertically with a homemade frame to access $B_\parallel > 1 \text{ T}$. A small B_\perp component is inevitably introduced when B_\parallel is applied due to imperfect vertical sample alignment. The B_x and B_y directions of the vector magnet are used to compensate the B_\perp component. The compensation is crucial for the measurements of large Pauli-limit violation of SC₃, because at $B_\parallel = 7 \text{ T}$ or so, an out-of-plane component $B_\perp \approx 0.1 - 0.2 \text{ mT}$ almost completely suppresses the superconductivity. Additionally, the cancellation of B_\perp gives an accurate R_{xx} dependence on B_\parallel and temperature so that the extraction of α in Fig. 4 is reliable.

Predictions of conventional depairing mechanisms for SC₁, SC₂, and SC₃: Here we summarize the main findings resulting from the conventional depairing mechanisms in the context of SC₁, SC₂, and SC₃, within the Ising superconductor framework^{17,51-53}. For SC₂, we find that experimentally determined values of α are not well reproduced by realistic values of $\lambda_R \lesssim 10 \text{ meV}$ (see SI, section 6). More precisely, conventional depairing theory would predict higher resilience (lower α by almost an order of magnitude) to the in-plane magnetic field. For the case of SC₁, we find that the conventional depairing theory applies well, explaining the large PVR. As such, another mechanism, like the interband-interaction scenario in the main text, must account for the relatively minor PVR in SC₂. The direction of B_\parallel can further shed light on the depairing mechanism. Theoretically, SC₁ is not sensitive to the in-plane field direction, as reported previously in Ref. 18. For SC₂, because both FP(2, 4) and FP(2, 2, 2) break the C_3 symmetry, we anticipate a dependence of T_c (or α) as the direction of B_\parallel is rotated. Experimentally, however, SC₂ shows no significant variation in T_c as the magnetic field is rotated (Extended Data Fig. 17), suggesting that this simple depairing picture relying on rigid occupancy of the trigonal-warping pockets should be revisited with a self-consistent Hartree-fock (HF) pairing analysis, where the Fermi surfaces adjust in response to the magnetic field. Finally, we also highlight that the mechanism discussed in the main text, the modification of interband and intraband interactions with an in-plane magnetic field, is entirely independent of the field direction. This is in accordance with the experimental observations, yet contrasts with the ‘‘conventional’’ depairing analysis.

Acknowledgments: We thank Jason Alicea, Étienne Lantagne-Hurtubise, Zhiyu Dong, Alex Thomson, Dmitry V. Chichinadze, Andrea Young, and Erez Berg for fruitful discussions.

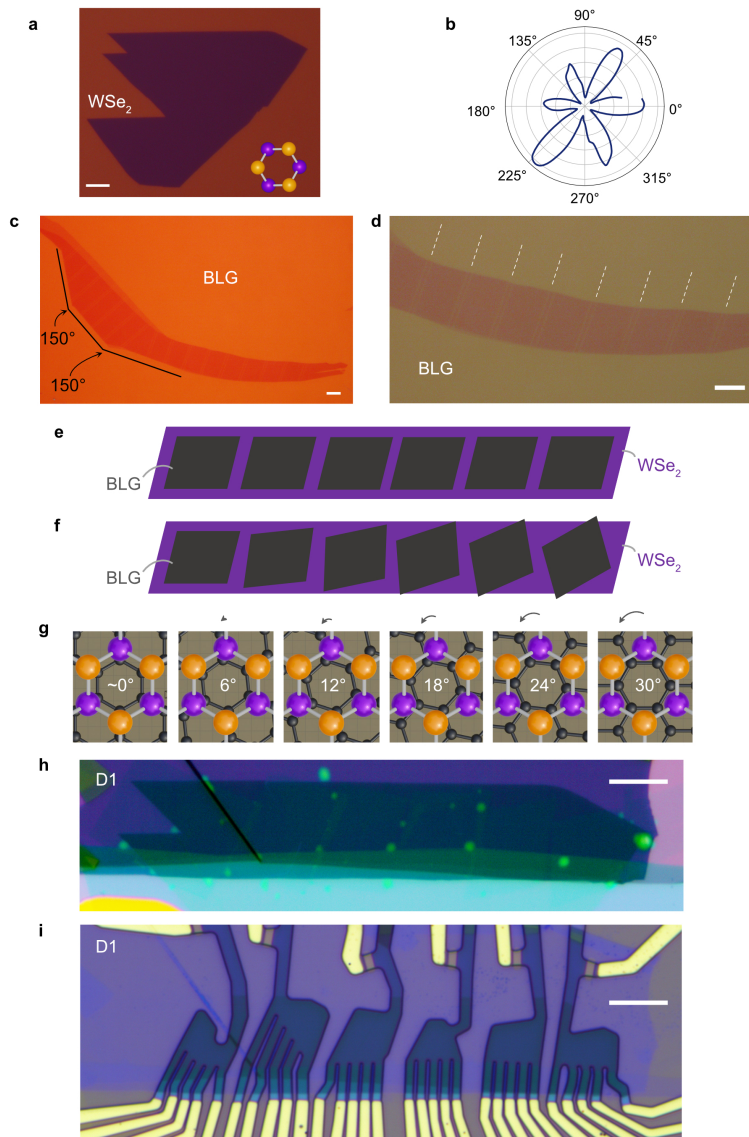
Funding: This work has been primarily supported by the Office of Naval Research (grant no. N142112635). S.N.-P. and D.H. also acknowledge the support of the Institute for Quantum Information and Matter, an NSF Physics Frontiers Center (PHY-2317110). G.S. acknowledges support from the Walter Burke Institute for Theoretical Physics at Caltech, and from the Yad Hanadiv Foundation through the Rothschild fellowship. H.M. and C.L. were supported by start-up funds from Florida State University and the National High Magnetic Field Laboratory. The National High Magnetic Field Laboratory is supported by the National Science Foundation through NSF/DMR-2128556 and the State of Florida. Y.O. and F.v.O. acknowledge support by Deutsche Forschungsgemeinschaft through CRC 183 (project C02). F.v.O. was further supported by Deutsche Forschungsgemeinschaft through a joint ANR-DFG project (TWISTGRAPH).

Author Contribution: Y.Z. and S.N.-P. designed the experiment. Y.Z. fabricated the devices, performed the measurements, and analyzed the data. Y.H. and D.H. performed the SHG measurements. G.S., H.M., C.L., F.v.O., and Y.O. developed theoretical models and performed calculations. K.W. and T.T. provided hBN crystals. S.N.-P. supervised the project. Y.Z., G.S., C.L., F.v.O., Y.O., and S.N.-P. wrote the manuscript with the input of other authors.

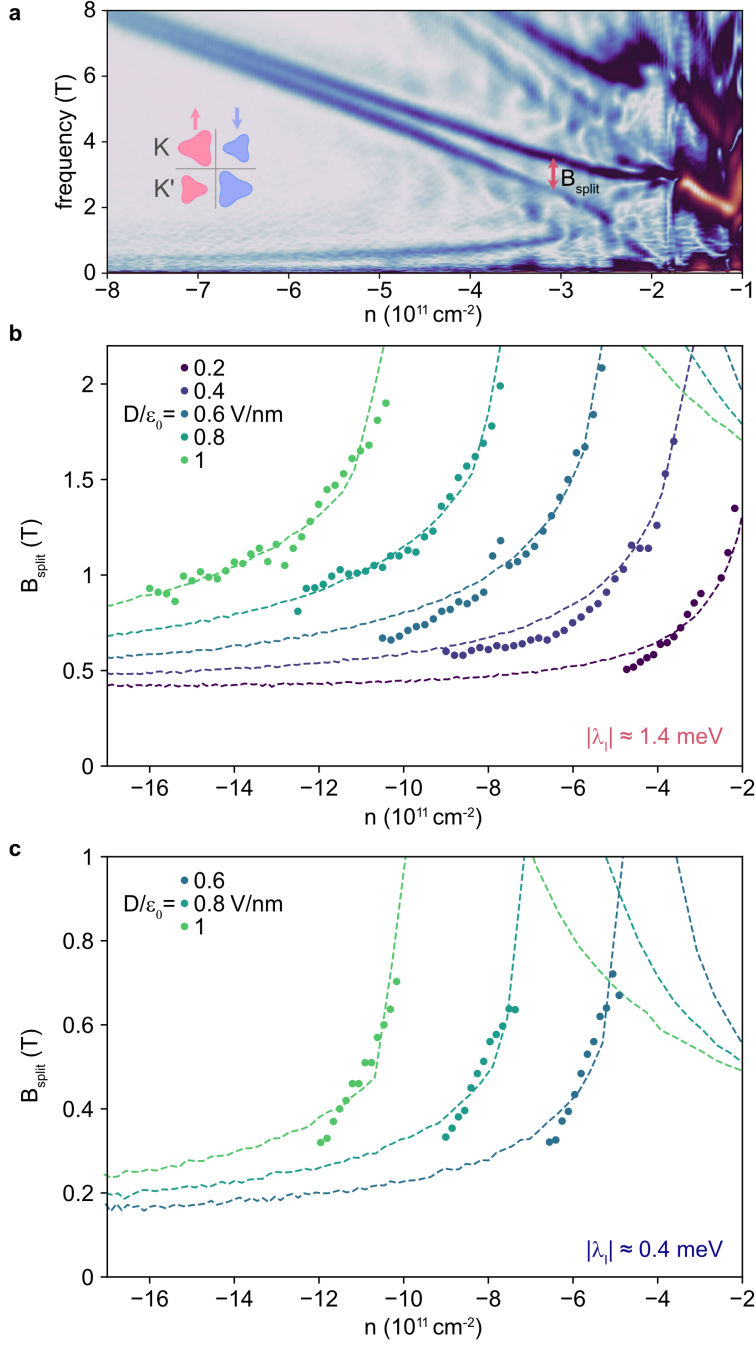
Competing interests: The authors declare no competing interests.

Data availability: The data supporting the findings of this study are available from the corresponding authors on reasonable request.

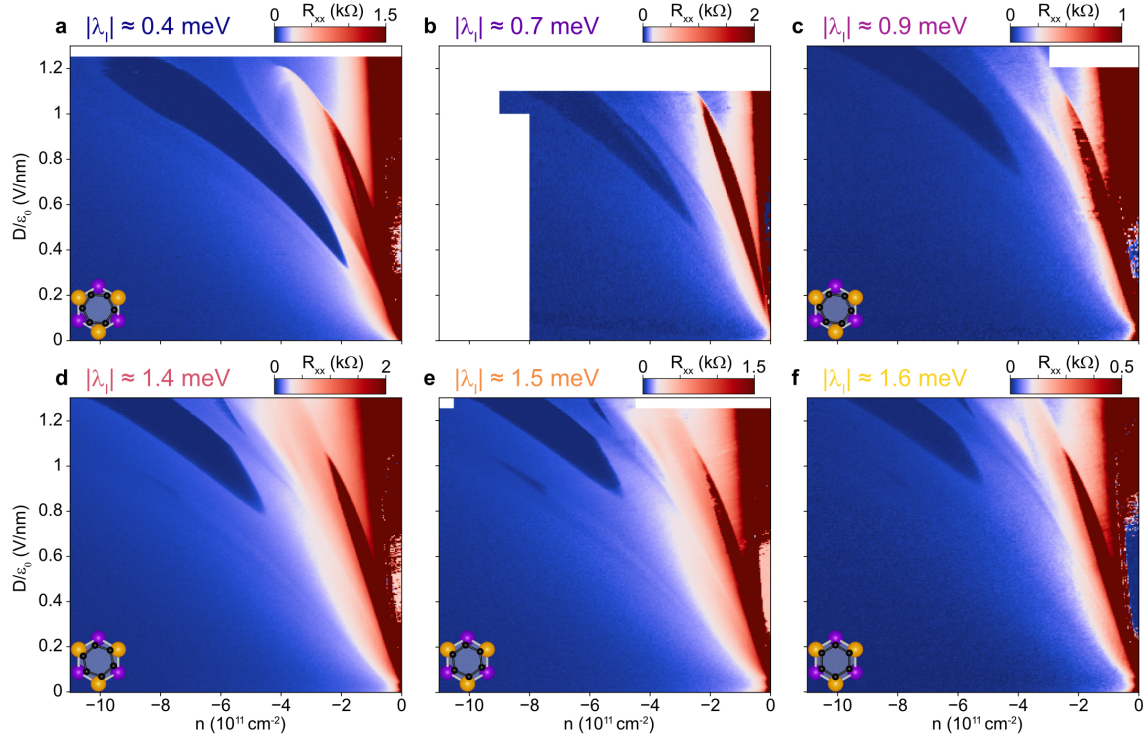
Code availability: All code used in modeling in this study is available from the corresponding authors on reasonable request.



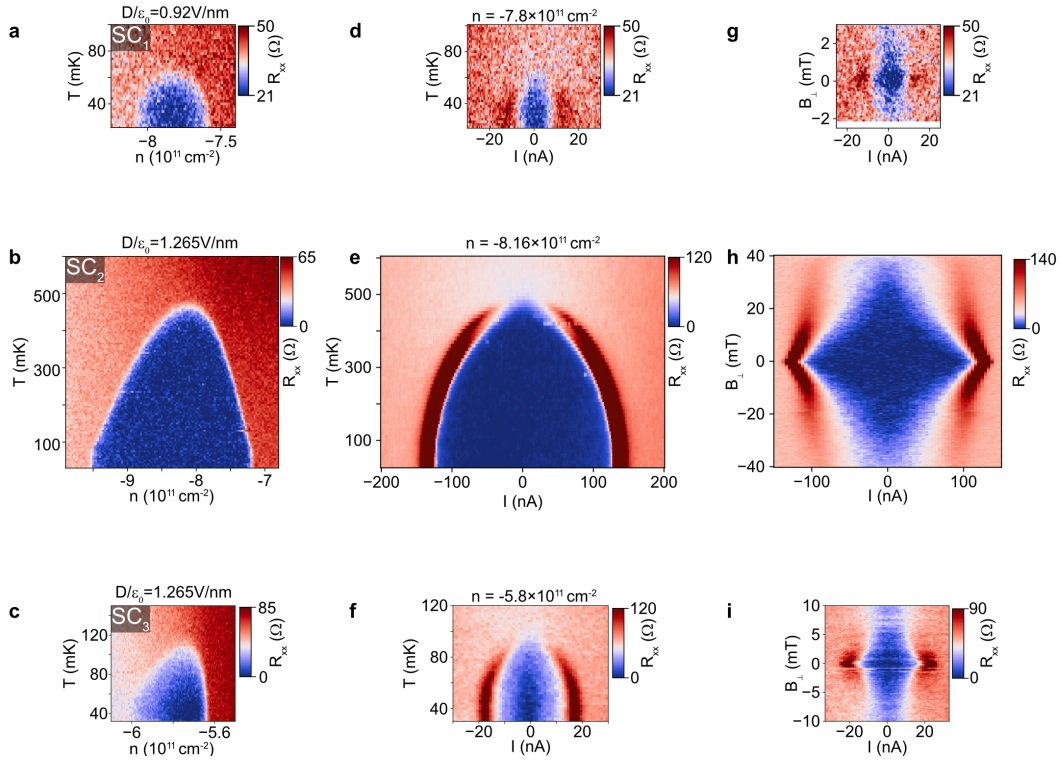
Extended Data Fig. 1 | Device fabrication for BLG-WSe₂ twisting. **a**, Optical image of a WSe₂ crystal. **b**, Second harmonic generation for the WSe₂ flake shown in **a**; the polarization of the incident and reflected beams are selected to lie parallel to the scattering plane. **c**, Optical image of a large BLG flake. Straight edges form angles 150° that are consistent with the three straight edges being along zigzag- or armchair-edge direction. **d**, Zoom-in image of the BLG in **c**, showing small BLG pieces that are separated by atomic-force-microscope-actuated cutting. **e-g**, Schematics showing the flake transferring processes for the continuous interfacial twisting. The BLG pieces are sequentially picked up with angles relative to WSe₂ in increments of 6°, from ~ 0° to 30°. **h**, Optical image of the twisting stack, clearly showing that the BLG pieces form different twist angles relative to the WSe₂ crystal. **i**, Optical image of the finished device set D1. All the scale bars correspond to 10 μm.



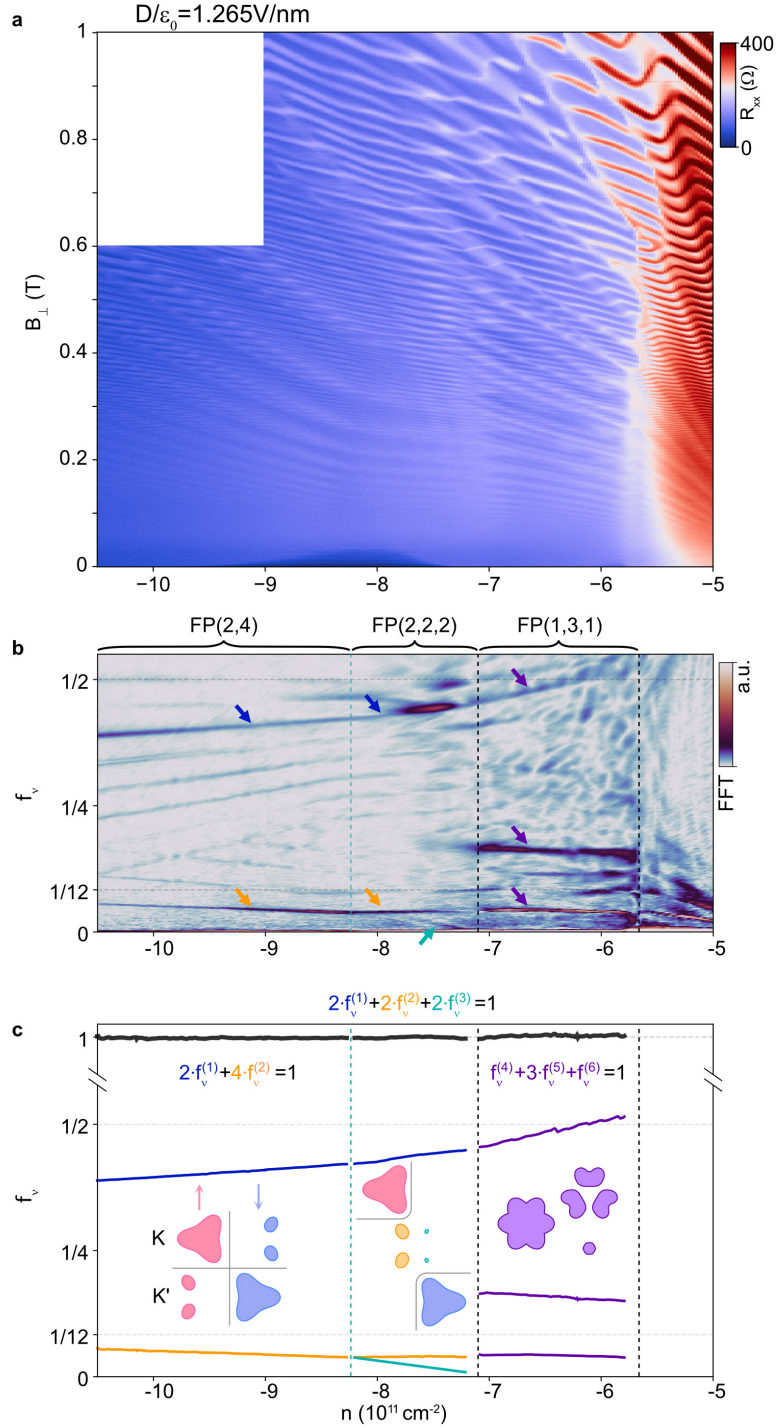
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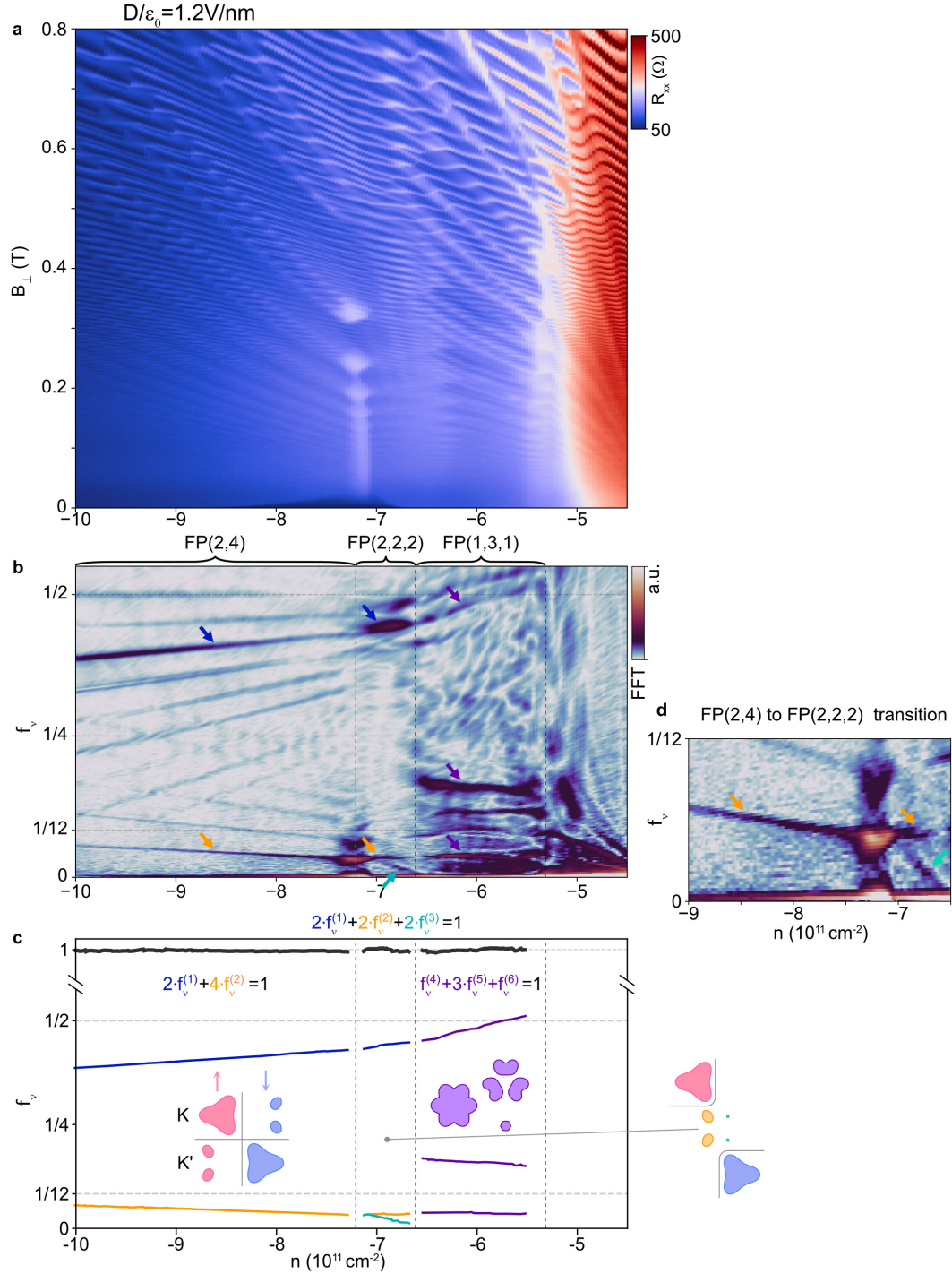
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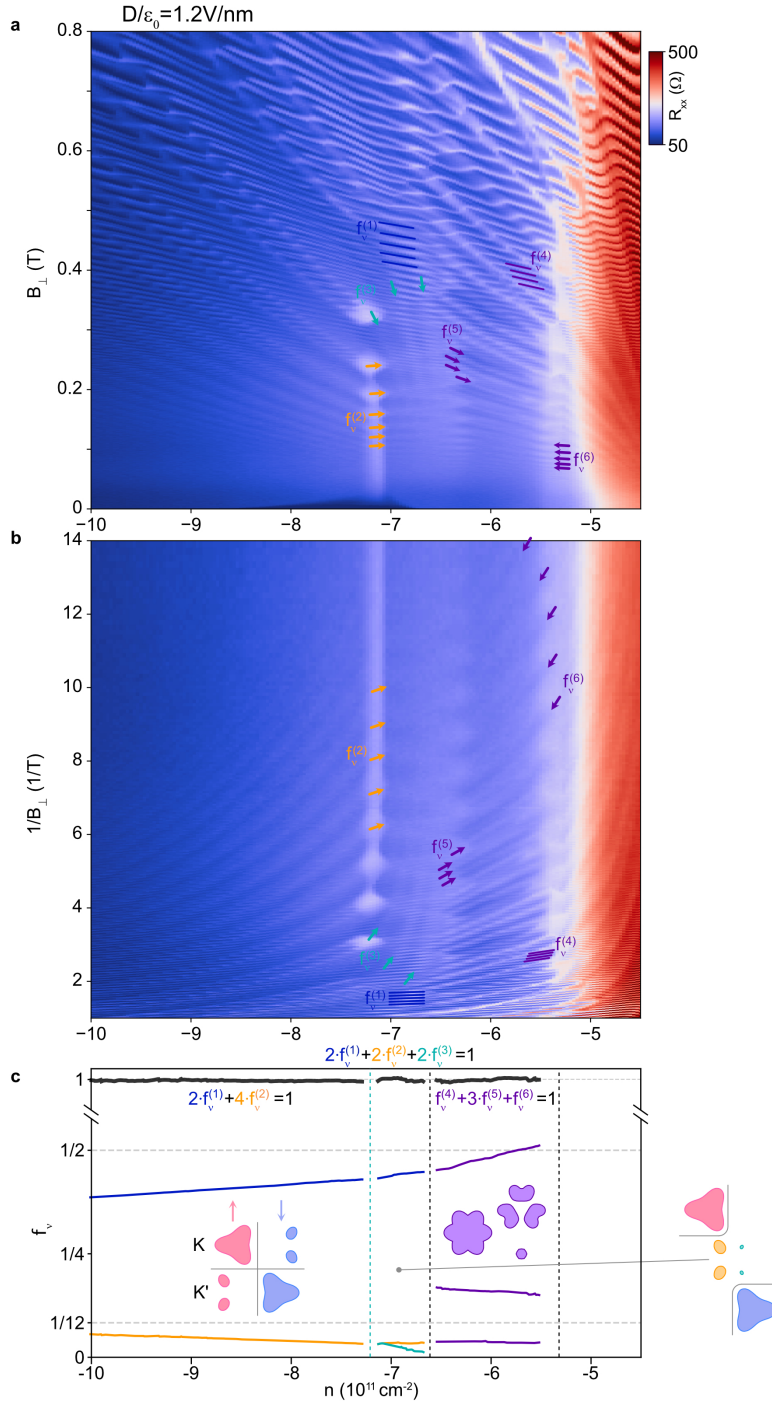
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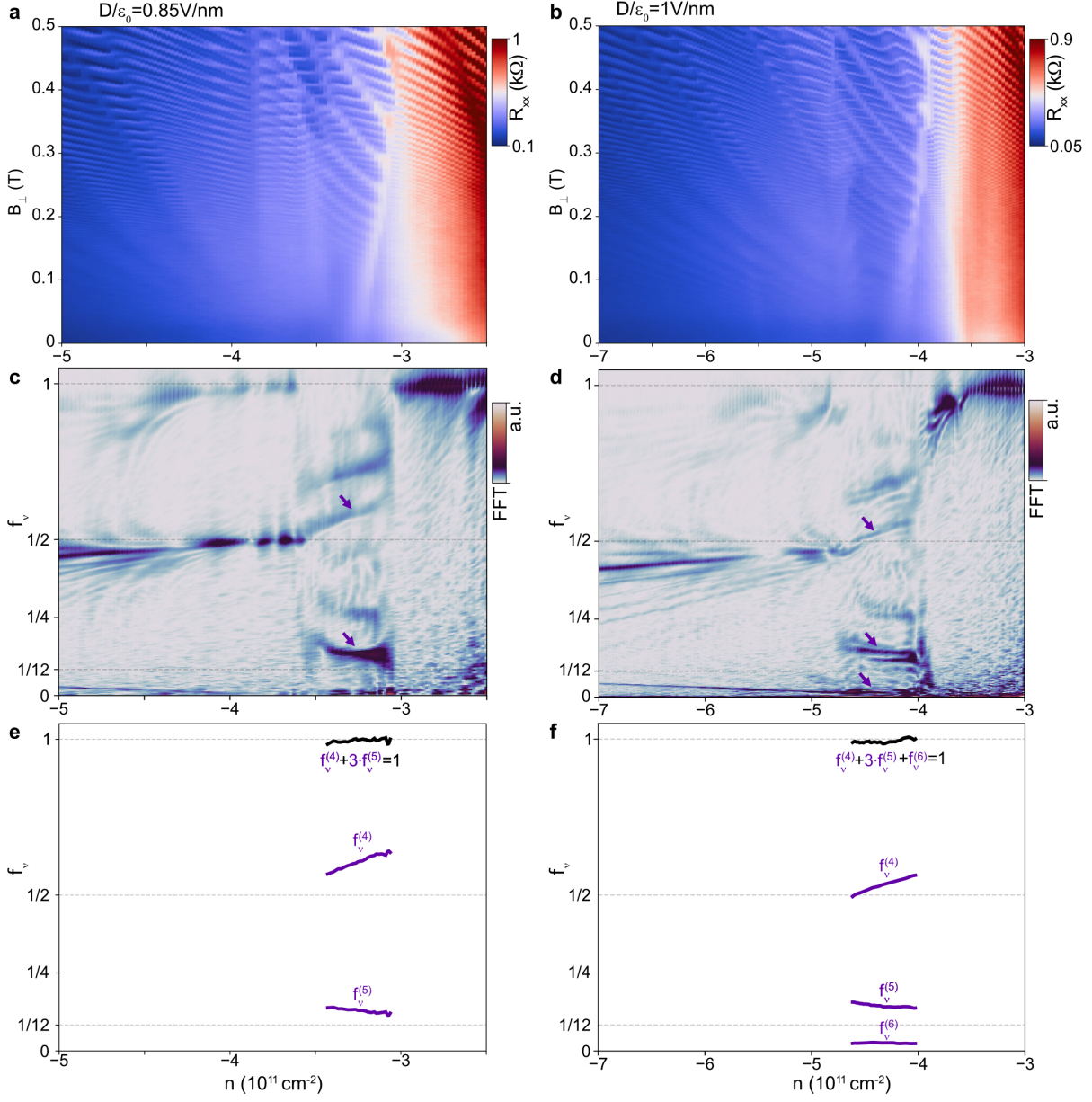
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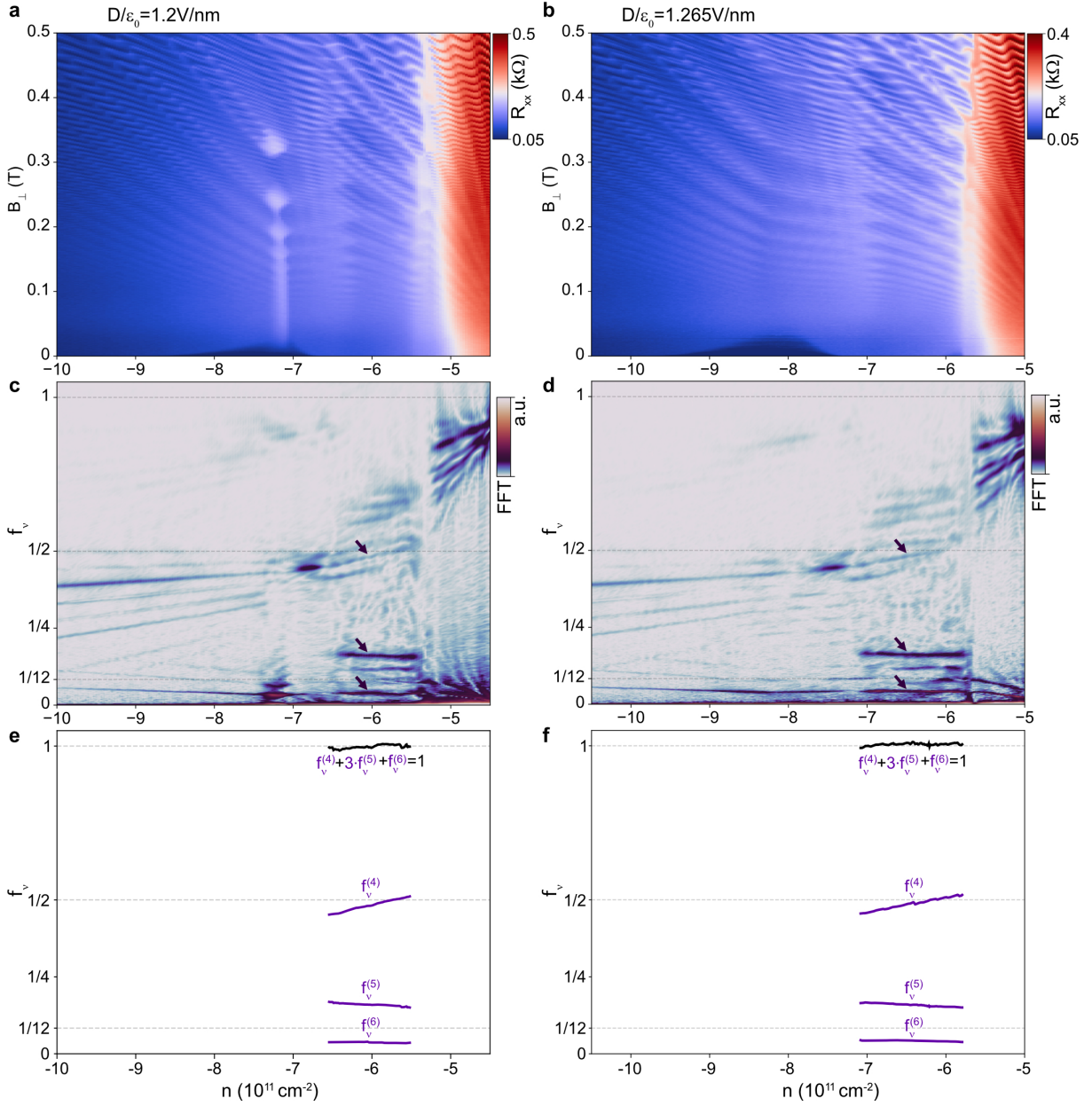
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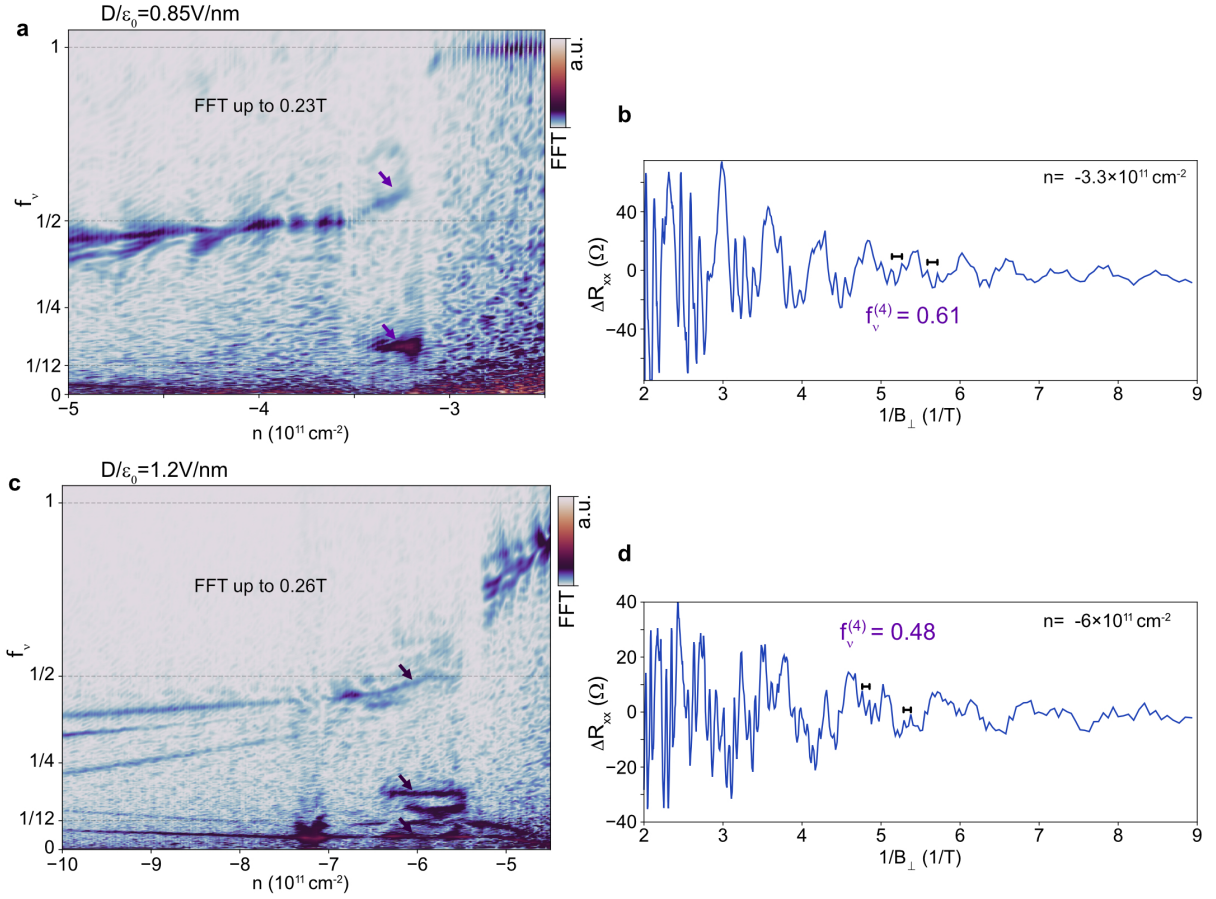
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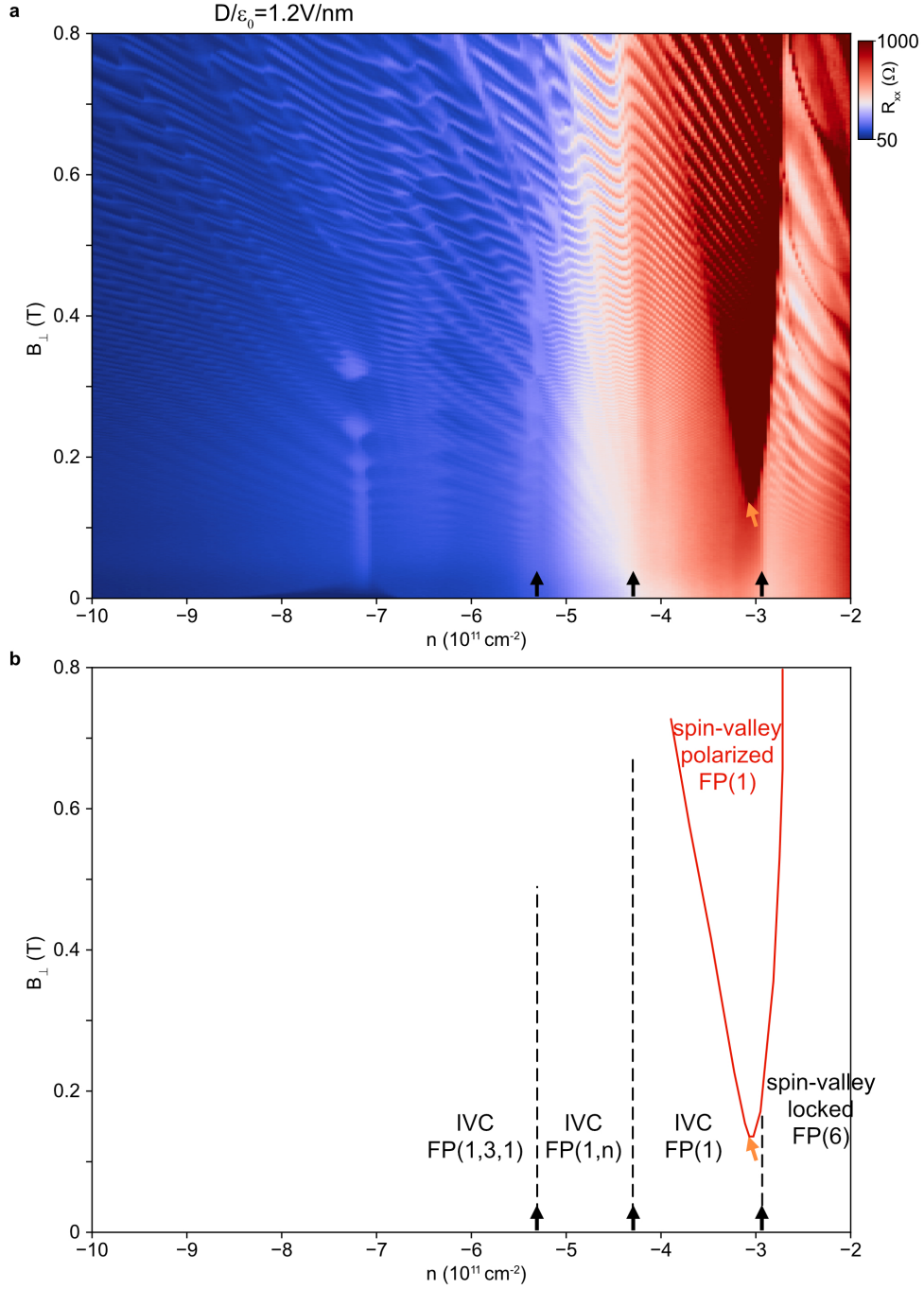
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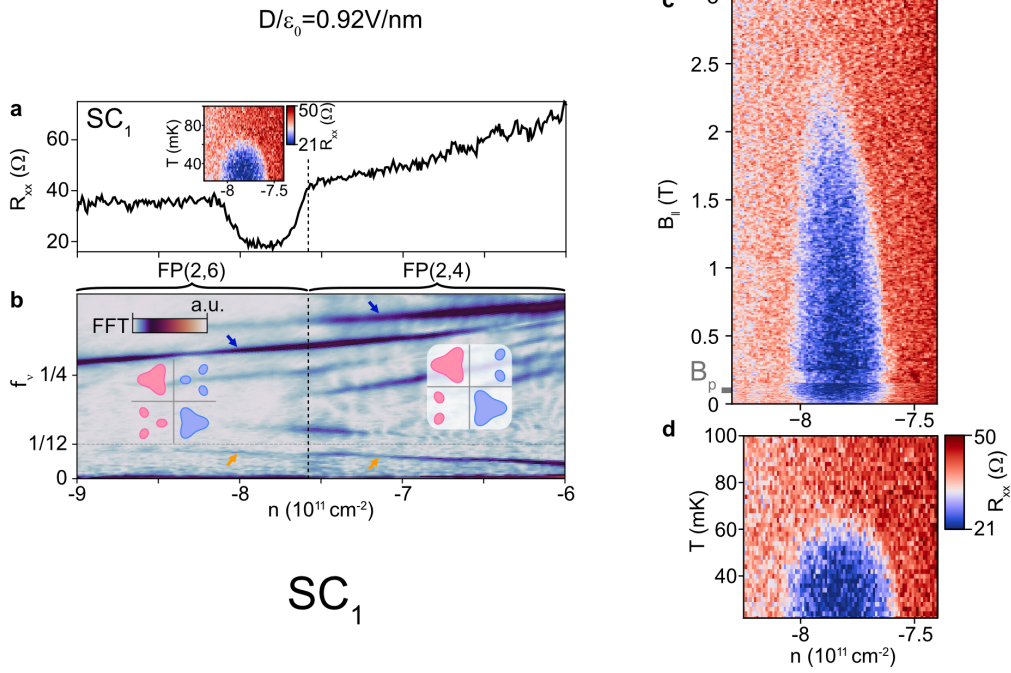
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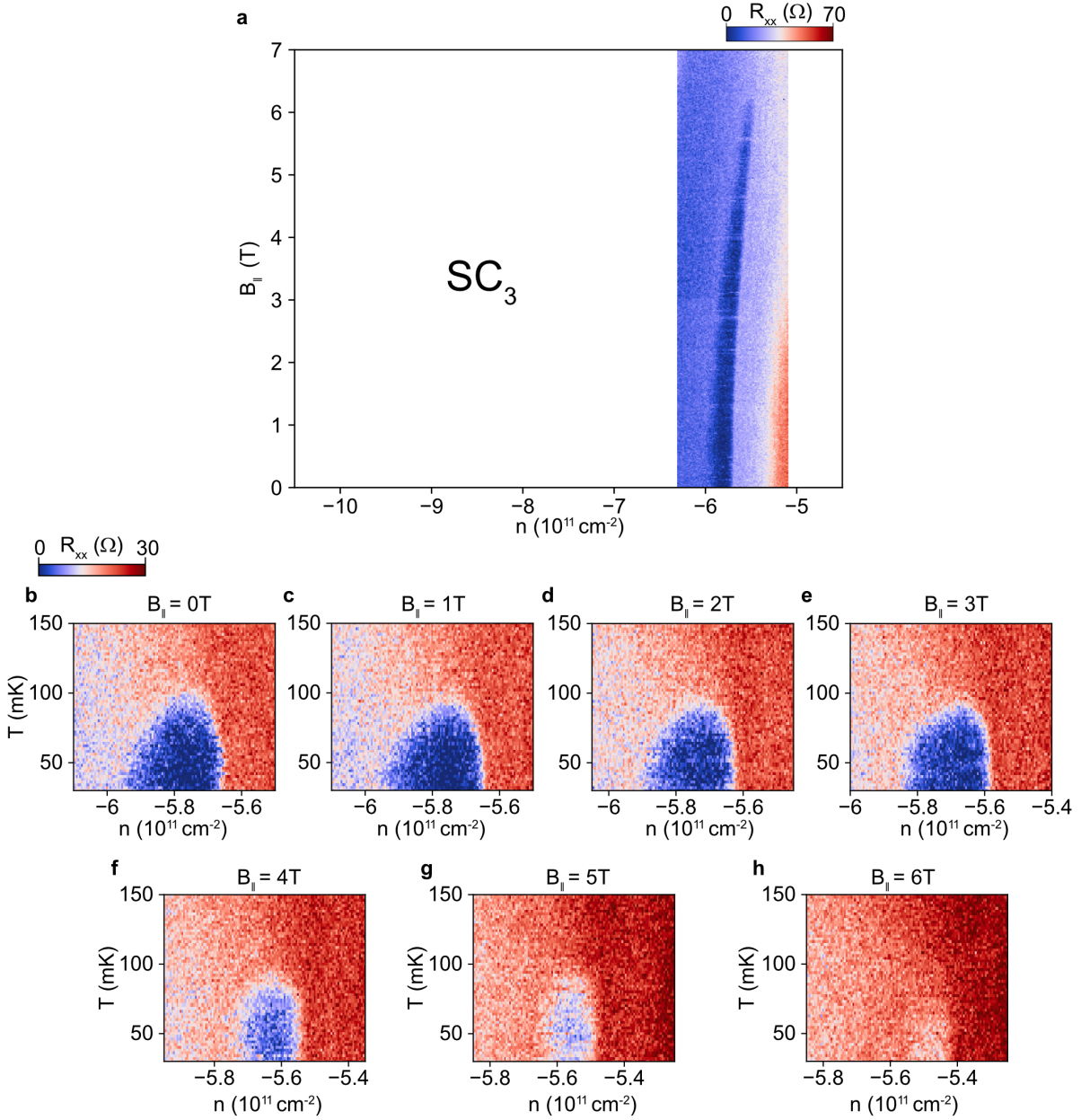
Extended Data Fig. 10 | FFT of FP(1, 3) and FP(1, 3, 1) with data at lower magnetic field. **a,c**, Frequency-normalized Fourier transform of $R_{xx}(1/B_{\perp})$ at $D/\epsilon_0 = 0.85 \text{ V/nm}$ (**a**) and 1.2 V/nm (**c**), respectively. The R_{xx} data are used up to 0.23 T and 0.26 T respectively. **b,d**, R_{xx} variation ΔR_{xx} as a function $1/B_{\perp}$ measured at $n = -3.3 \times 10^{11} \text{ cm}^{-2}$, $D/\epsilon_0 = 0.85 \text{ V/nm}$ (**b**) and $n = -6 \times 10^{11} \text{ cm}^{-2}$, $D/\epsilon_0 = 1.2 \text{ V/nm}$ (**d**), respectively.



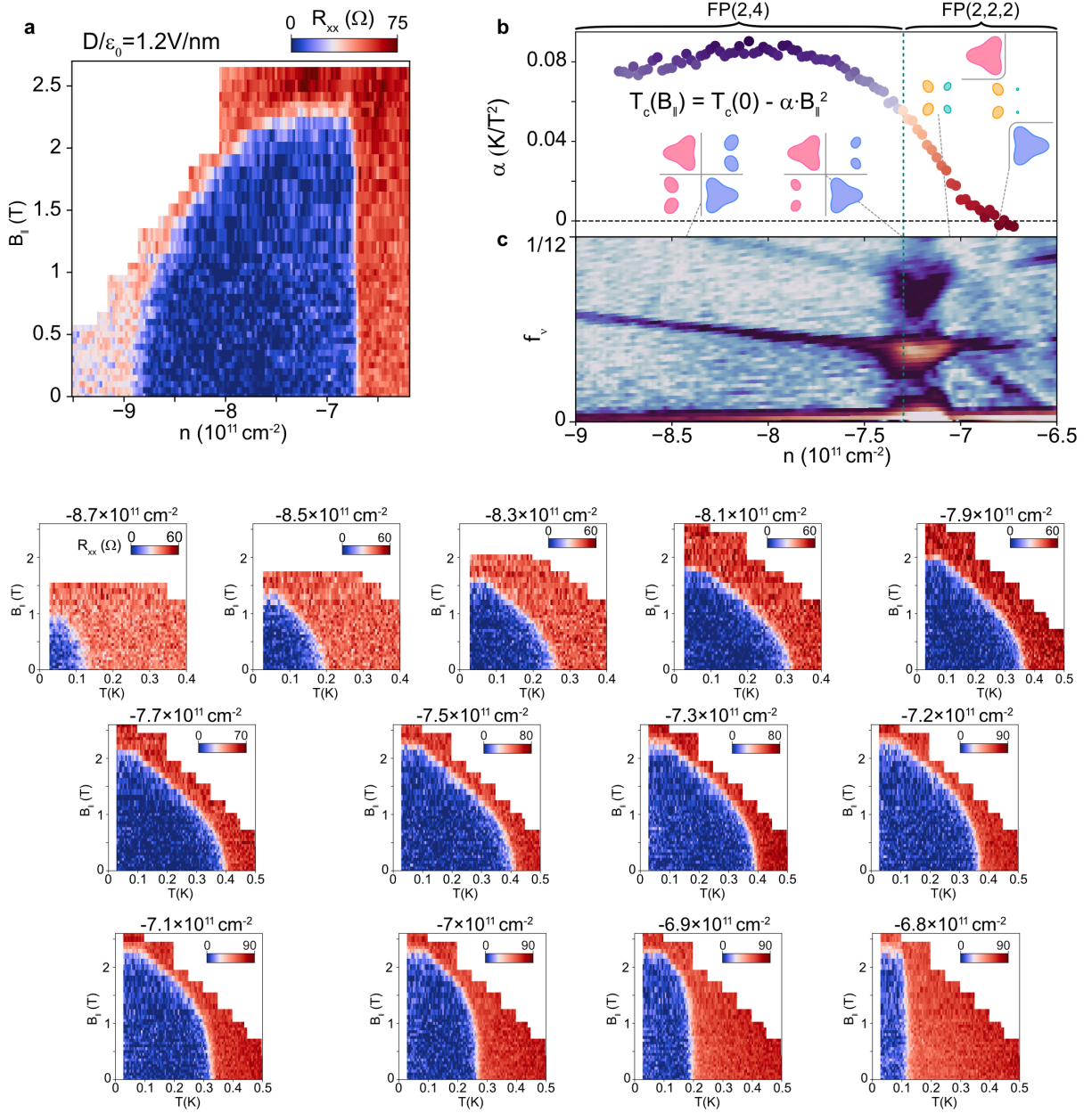
Extended Data Fig. 11 | Evolution of phase boundaries as a function of B_{\perp} . **a**, R_{xx} versus out-of-plane magnetic field B_{\perp} and doping density n measured at $D/\epsilon_0 = 1.2 \text{ V/nm}$ for a device with $|\lambda_I| \approx 1.5 \text{ meV}$. Phase boundaries are marked out in **b**. The black arrows and dashed lines mark the phase boundaries that are not sensitive to B_{\perp} , suggestive of inter-valley coherence with little or no net orbital moments. The red line draws the phase boundary of the spin-valley polarized FP(1); the boundary grows (orange arrow) with B_{\perp} due to large orbital moments.



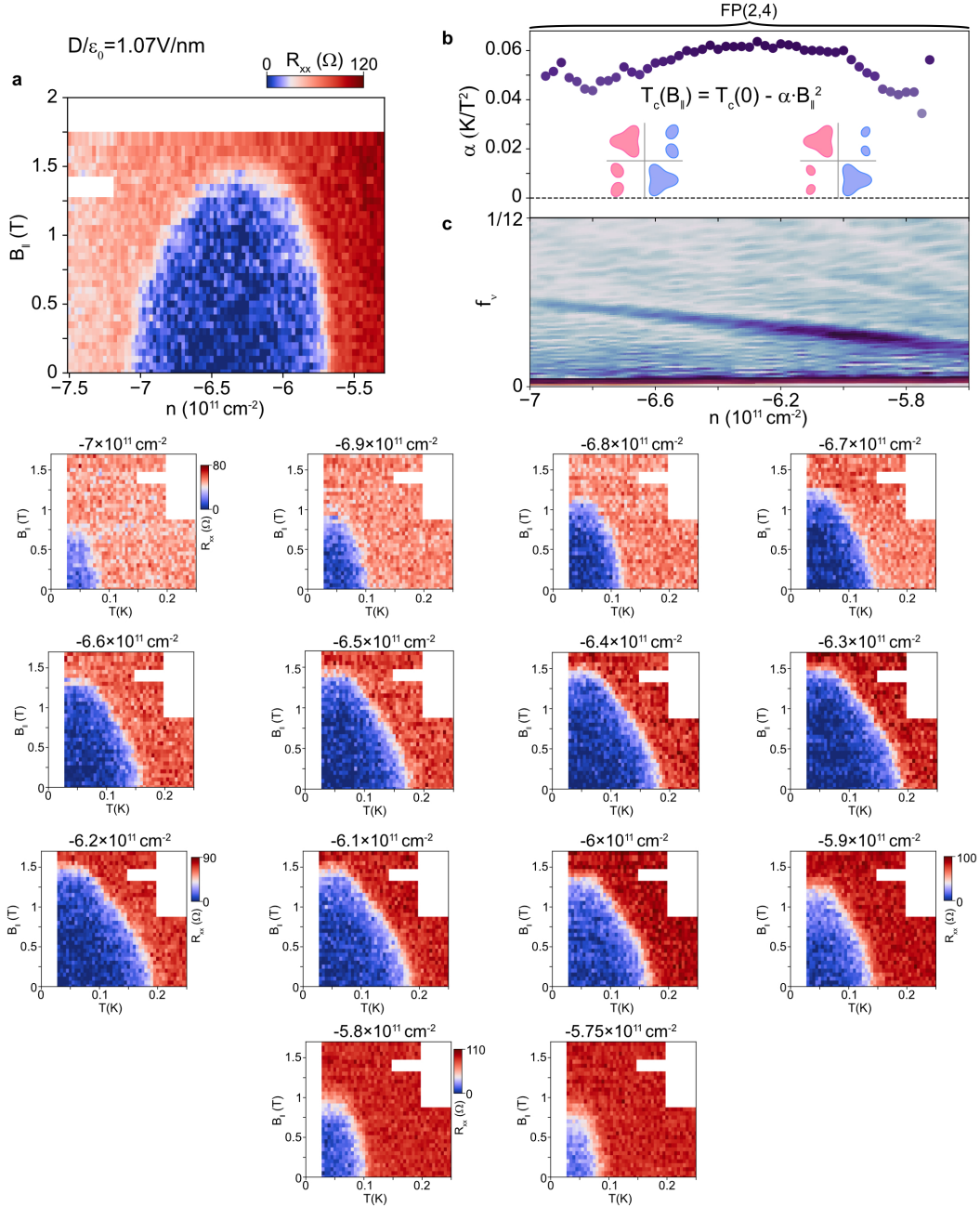
Extended Data Fig. 12 | B_{\parallel} dependence of SC₁. **a**, R_{xx} versus n measured at $D/\epsilon_0 = 0.92 \text{ V/nm}$. Inset shows R_{xx} versus n and temperature for the superconducting dome SC₁. **b**, Frequency-normalized FFT of $R_{xx}(1/B_{\perp})$ over the same doping range as in **a**. **c,d**, n -dependent R_{xx} versus in-plane magnetic field (**c**) or versus temperature (**d**), showing the disappearance of SC₁. The grey bar marks the Pauli limit B_p .



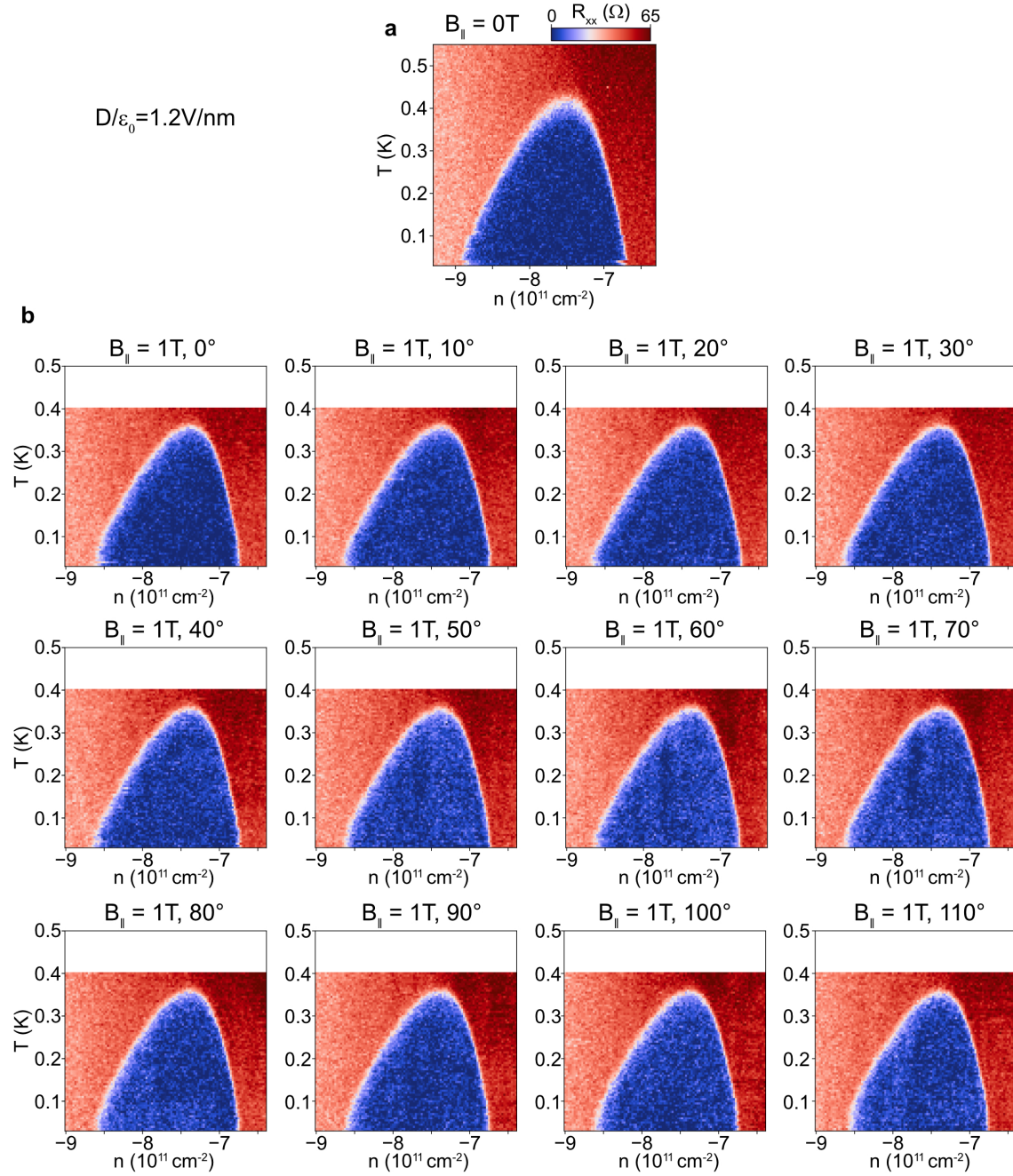
Extended Data Fig. 13 | B_{\parallel} dependence of SC_3 . **a**, R_{xx} versus doping density n and in-plane magnetic field B_{\parallel} showing the evolution of SC_3 . **b-h**, R_{xx} versus doping density n and temperature measured from $B_{\parallel} = 0 \text{ T}$ (**b**) to 6 T (**h**), 1 T increment step.



Extended Data Fig. 15 | B_{\parallel} dependence of SC_2 at $D/\epsilon_0 = 1.2 \text{ V/nm}$. **a**, R_{xx} versus doping and B_{\parallel} focusing around SC_2 at $D/\epsilon_0 = 1.2 \text{ V/nm}$. **b**, Fitting coefficient α versus doping density n for SC_2 at the same D . **c**, Frequency-normalized Fourier transform of $R_{xx}(1/B_{\perp})$ over the same doping range as in **b**, focusing around low frequencies representing the two types of trigonal-warped pockets. Bottom panels show R_{xx} versus temperature and B_{\parallel} at different doping for $D/\epsilon_0 = 1.2 \text{ V/nm}$.



Extended Data Fig. 16 | B_{\parallel} dependence of SC_2 at $D/\epsilon_0 = 1.07$ V/nm. **a**, R_{xx} versus doping and B_{\parallel} focusing around SC_2 at $D/\epsilon_0 = 1.07$ V/nm. **b**, Fitting coefficient α versus doping density n for SC_2 at the same D . **c**, Frequency-normalized Fourier transform of $R_{xx}(1/B_{\perp})$ over the same doping range as in **b**, focusing around low frequencies representing the single type of trigonal-warping pockets without nematic redistribution of holes. Bottom panels show R_{xx} versus temperature and B_{\parallel} at different doping at $D/\epsilon_0 = 1.07$ V/nm. At this D field, SC_2 doesn't onset from FP(2, 2, 2). The rapidly changing α with diminished values are accordingly absent.



Extended Data Fig. 17 | Isotropic B_{\parallel} dependence of SC_2 . **a**, R_{xx} versus n and temperature showing SC_2 at $D/\epsilon_0 = 1.2 \text{ V/nm}$. **b**, R_{xx} versus n and temperature showing SC_2 , measured with an in-plane magnetic field $B_{\parallel} = 1 \text{ T}$, at different in-plane angles. The depairing of SC_2 is isotropic along different B_{\parallel} directions.

Supplementary Information:

Twist-Programmable Superconductivity in Spin-Orbit Coupled Bilayer Graphene
Yiran Zhang, Gal Shavit, Huiyang Ma, Youngjoon Han, Kenji Watanabe, Takashi Taniguchi, David Hsieh, Cyprian Lewandowski, Felix von Oppen, Yuval Oreg, and Stevan Nadj-Perge

1 Importance of interband superconductivity in BLG

Much of the experimental observations in BLG proximitized by WSe_2 may be understood in the context of multiband superconductivity. Here, the bands correspond to the majority and minority bands are split by the Ising spin-orbit coupling (ISOC), possibly further enhanced by electron-electron interactions. It is the coupling between these two sectors (majority and minority bands) in the Cooper channel, i.e., pair scattering between the bands, that is crucial to interpreting the experimental results.

The delayed onset (in terms of higher displacement fields) of superconductivity in the main dome when the spin-orbit coupling is increased is elucidated in Sec. 4. When the density of states (DOS) of both bands is high near the Fermi level, screening of the bare Coulomb repulsion becomes much more efficient, enabling superconductivity mediated by some retarded attraction. As the bands are further split by the ISOC, *the band-concurrent high DOS region is pushed to higher displacement fields*. This is illustrated in SI Fig. 1.

The large variance in the behavior of the different superconducting region when an in-plane magnetic field is introduced, as manifested in varying Pauli-limit-violation ratios, is discussed in Sec. 5. We consider the effect of a Zeeman term in *gradually decoupling the majority and minor bands in the Cooper channel*. Analysing the energetics of spin magnetization in the presence of both ISOC and Hund's coupling, we illustrate how the main superconducting dome, where the imbalance between majority and minority carriers is the greatest, becomes most vulnerable to this effect. We further demonstrate the experimental trends are well understood within our modeling. We stress that the Zeeman coupling is not assumed to have any pair-breaking role, the effect we consider is purely due to "shifting" interaction strength from the intraband part of the coupling matrix to the interband part. In Sec. 6, we consider a more direct depairing model and contrast with the results of the proposed mechanism here.

Finally, we note that in our analysis we do not specify or rely on what is the pairing glue which mediates superconductivity. We remain agnostic with regards to its origin, as well as its intra-band/interband nature, which do not modify our conclusions.

2 Variational Hartree-Fock

We begin by calculating the the non-interacting band structure of biased Bernal-stacked bilayer graphene. Expanded around the valley K/K' points in momentum space, the Hamiltonian is ³⁷

$$H_{BLG} = \sum_{\mathbf{k}, \tau, s} c_{\tau s \mathbf{k}}^\dagger h_\tau(\mathbf{k}) c_{\tau s \mathbf{k}}, \quad (1)$$

with $c_{\tau s \mathbf{k}} = (A_{1, \tau s \mathbf{k}}, B_{1, \tau s \mathbf{k}}, A_{2, \tau s \mathbf{k}}, B_{2, \tau s \mathbf{k}})^T$, where $X_{i, \tau s \mathbf{k}}$ annihilates an electron on sub-lattice X in layer i , with spin s , and momentum \mathbf{k} near the valley τ . The matrix h_τ is given by

$$h_\tau(\mathbf{k}) = \begin{pmatrix} \frac{U}{2} & v_0 \Pi_\tau^* & -v_4 \Pi_\tau^* & -v_3 \Pi_\tau^* \\ v_0 \Pi_\tau & \frac{U}{2} + \Delta' & \gamma_1 & -v_4 \Pi_\tau^* \\ -v_4 \Pi_\tau & \gamma_1 & -\frac{U}{2} + \Delta' & v_0 \Pi_\tau^* \\ -v_3 \Pi_\tau^* & -v_4 \Pi_\tau & v_0 \Pi_\tau & -\frac{U}{2} \end{pmatrix}, \quad (2)$$

with $\Pi_\tau = \tau k_x + i k_y$, and the parameters $v_i = \frac{\sqrt{3}}{2} a \gamma_i$, $a = 0.246$ nm, $\gamma_0 = 2.61$ eV, $\gamma_1 = 361$ meV, $\gamma_3 = 283$ meV, $\gamma_4 = 138$ meV, and $\Delta' = 15$ meV⁵⁶. The interlayer potential difference U is approximately $U \approx -dD/\epsilon$, where the interlayer distance is $d \approx 0.33$ nm, $\epsilon \approx 4.3$, and D is the displacement field. We diagonalize H_{BLG} at each momentum, and extract the dispersion relation of the lowest-lying valence band, which we denote by $\epsilon_{\tau, \mathbf{k}}$.

Our analysis proceeds with a phenomenological description of the underlying physics of electrons in this band in the spirit of Ref. 57, described by the 4-spinor $\Psi_{\mathbf{k}}$ of fermionic annihilation operators at momentum \mathbf{k} , with valley and spin degrees of freedom, described by Pauli matrices τ_i and s_i , respectively. We analyze the Hamiltonian,

$$H = H_0 + H_{\text{ISOC}} + H_{\text{int}}, \quad (3)$$

$$H_0 = \sum_{\mathbf{k}} \Psi_{\mathbf{k}}^\dagger \left(\epsilon_{+, \mathbf{k}} \frac{1 + \tau_z}{2} + \epsilon_{-, \mathbf{k}} \frac{1 - \tau_z}{2} \right) \Psi_{\mathbf{k}}, \quad (4)$$

$$H_{\text{ISOC}} = \sum_{\mathbf{k}} \Psi_{\mathbf{k}}^\dagger \lambda_0 \tau_z s_z \Psi_{\mathbf{k}}, \quad (5)$$

$$H_{\text{int}} = \frac{1}{\Omega} \sum_{\mathbf{q}} \left(\frac{U_C}{2} N_{\mathbf{q}} N_{-\mathbf{q}} + U_V n_{\mathbf{q}}^+ n_{-\mathbf{q}}^- + J \mathbf{S}_{\mathbf{q}}^+ \cdot \mathbf{S}_{-\mathbf{q}}^- \right), \quad (6)$$

where $N_{\mathbf{q}} = \sum_{\mathbf{k}} \Psi_{\mathbf{k}+\mathbf{q}}^\dagger \Psi_{\mathbf{k}}$, $n_{\mathbf{q}}^\pm = \sum_{\mathbf{k}} \Psi_{\mathbf{k}+\mathbf{q}}^\dagger \frac{1 \pm \tau_z}{2} \Psi_{\mathbf{k}}$, $\mathbf{S}_{\mathbf{q}}^\pm = \sum_{\mathbf{k}} \Psi_{\mathbf{k}+\mathbf{q}}^\dagger \frac{1 \pm \tau_z}{2} \mathbf{s} \Psi_{\mathbf{k}}$, and Ω is the system area. The term proportional to λ_0 is the bare Ising-type spin-orbit coupling induced in the valence band (at positive values of the electric displacement field) by the proximity to WSe₂. The structure of H_{int} is the most general form of short-range interactions which respect the symmetry of the system: time-reversal, $SU(2)$ spin symmetry (in the absence of magnetic fields or spin-orbit coupling), and the $U(1)$ charge and (approximate) valley symmetries. The interaction term

proportional to U_C is a structure-less density-density interaction, which is entirely $SU(4)$ symmetric in valley-spin space, and is considered to be dominant as compared to the other two terms. The term proportional to U_V accounts for possible differences between intravalley and intervalley density-density interactions and will be set to zero throughout this work, as it is non-essential for correctly capturing the phenomenology we aim to study. Finally, J is the intervalley Hund's coupling between electron spins in opposite valleys.

Although the Ising spin-orbit coupling term H_{ISOC} explicitly breaks the flavor symmetry of the system, i.e., not all spin-valley flavors are populated equally even in the absence of interactions, the presence of non-negligible interactions in H_{int} may significantly alter the non-interacting picture. We employ a variational Hartree-Fock procedure to resolve the different flavor-resolved fillings. Our analysis thus proceeds as follows. At a given chemical potential μ , the grand-potential $\Phi = \langle H - \mu N_0 \rangle_{\text{H.F.}}$ is minimized, where $\langle \rangle_{\text{H.F.}}$ denotes the expectation value calculated using the variational wavefunction,

$$|\Psi\rangle_{\text{H.F.}} = \prod_{\tau,s} \left(\prod_{\substack{\mathbf{k} \\ \epsilon_{\mathbf{k}} > \mu_{\tau,s}}} \sum_{s'} \mathcal{U}(\tau\theta)_{ss'} \psi_{\mathbf{k},\tau,s'} \right) |\text{CN}\rangle, \quad (7)$$

where $\psi_{\tau,s,\mathbf{k}}$ annihilates an electron in valley τ and spin s in the valence band at momentum \mathbf{k} with energy $\epsilon_{\mathbf{k}}$, $|\text{CN}\rangle$ is the flavor-symmetric charge-neutral Fermi-sea, and $\mu_{\tau,s} \leq 0$ are the four variational parameters corresponding to the four spin-valley flavors. The possibility of canting in the different valleys is captured by the matrix $\mathcal{U}(\theta) = \begin{pmatrix} \cos \frac{\theta}{2} & \sin \frac{\theta}{2} \\ -\sin \frac{\theta}{2} & \cos \frac{\theta}{2} \end{pmatrix}$. Notice that full canting, i.e., alignment of the majority and minority bands according to their spin polarization corresponds to $\theta = \pi/2$, whereas spin-valley locking corresponds to $\theta = 0$ (no canting).

Obtaining the different μ_i , we calculate the flavor resolved densities $\nu_i = -\frac{1}{\Omega} \sum_{\substack{\mathbf{k} \\ \mu_i < \epsilon_{\mathbf{k}} < 0}}$, i.e., (minus) the number of \mathbf{k} points in the valence band whose energies are larger than μ_i . The total density is thus $n = \sum_i \nu_i$. The resultant Hartree-Fock Hamiltonian (up to additional constant contributions) can thus be written as

$$H_{\text{HF}} = \sum_{\tau s \mathbf{k}} \psi_{\tau s \mathbf{k}}^\dagger (\epsilon_{\tau \mathbf{k}} - \mu_{\tau s}) \psi_{\tau s \mathbf{k}}. \quad (8)$$

3 Multiband superconductivity framework

The starting point we consider for analyzing superconductivity in this work is an electronic system with two bands, with each band being two-fold degenerate (in the present case due to spin). We are interested in Cooper-channel interactions, and restrict ourselves to a superconducting gap with

trivial symmetry. In that case, the usual mean-field ansatz for the order parameter assumes a vector form due to the multiband nature of the problem,

$$\Delta = \begin{pmatrix} \Delta_1 \\ \Delta_2 \end{pmatrix} = \begin{pmatrix} g & g_x \\ g_x & g \end{pmatrix} \left\langle \left(\frac{1}{\Omega} \sum_{\mathbf{k}} \psi_{-\mathbf{k}1+} \psi_{\mathbf{k}1-} \right) \right\rangle \equiv \hat{g}_{\text{initial}} \left\langle \left(\frac{1}{\Omega} \sum_{\mathbf{k}} \psi_{-\mathbf{k}1+} \psi_{\mathbf{k}1-} \right) \right\rangle, \quad (9)$$

where Ω is the system volume, $\psi_{\mathbf{k},n,p}$ annihilates an electron with momentum \mathbf{k} , in band $n = 1, 2$, and internal flavor $p = \pm$. We assume \hat{g}_{initial} is a matrix of repulsive interactions, originating from the intrinsic (presumably Thomas-Fermi screened) Coulomb interaction. For reasons which are clarified below, we take the intraband repulsion g to be the same in both bands, though a generalization is straightforward within our analysis.

Given the form of Δ , the mean-field BCS Hamiltonian takes the form

$$H_{\text{BCS}} = \sum_{\mathbf{k},n,p} \xi_{\mathbf{k}np} \psi_{\mathbf{k}np}^\dagger \psi_{\mathbf{k}np} + \sum_{\mathbf{k}} (\Delta_1^* \psi_{-\mathbf{k}1+} \psi_{\mathbf{k}1-} + \Delta_2^* \psi_{-\mathbf{k}2+} \psi_{\mathbf{k}2-} + \text{h.c.}) + \Omega \Delta^\dagger (\hat{g}_{\text{initial}})^{-1} \Delta, \quad (10)$$

and $\xi_{\mathbf{k}np}$ represents the normal-state energy of the n, p band relative to the Fermi energy.

Our analysis will generally consist of three steps, detailed below.

Tolmachev-Anderson-Morel step We introduce an energy scale ω^* , below which some retarded interaction is activated. Clearly, this approach, following Tolmachev²⁸, and Morel and Anderson²⁹, is another significant simplification of what should generally be an energy-dependent interaction in the Cooper channel, yet it is sufficient to illustrate all our key results. In the path-integral formalism, we integrate out the electrons with energy greater than ω^* ⁵⁸, obtaining the renormalized interaction matrix,

$$\hat{g}_{\text{TAM}}(\omega^*) = \left[(\hat{g}_{\text{initial}})^{-1} + \begin{pmatrix} \ell_1 & \\ & \ell_2 \end{pmatrix} \right]^{-1}, \quad (11)$$

where we have defined

$$\ell_n = \left\{ \int_{\omega^*}^{\infty} + \int_{-\infty}^{-\omega^*} \right\} d\xi \frac{\mathcal{N}_n(\xi)}{|\xi|}, \quad (12)$$

where $\mathcal{N}_n(\xi)$ is the DOS of the n -band at a distance ξ away from the Fermi level. We may explicitly write the elements of this matrix,

$$\hat{g}_{\text{TAM}}(\omega^*) = \begin{pmatrix} \frac{g+\ell_2(g^2-g_x^2)}{1+g(\ell_1+\ell_2)+(g^2-g_x^2)\ell_1\ell_2} & \frac{g_x}{1+g(\ell_1+\ell_2)+(g^2-g_x^2)\ell_1\ell_2} \\ \frac{g_x}{1+g(\ell_1+\ell_2)+(g^2-g_x^2)\ell_1\ell_2} & \frac{g+\ell_1(g^2-g_x^2)}{1+g(\ell_1+\ell_2)+(g^2-g_x^2)\ell_1\ell_2} \end{pmatrix} \equiv \begin{pmatrix} u_1 & u_x \\ u_x & u_2 \end{pmatrix}. \quad (13)$$

For the sake of illustration, consider two limiting cases. If the different bands are decoupled, $g_x = 0$, we find

$$\hat{g}_{\text{TAM}}(\omega^*) = \begin{pmatrix} \frac{g}{1+g\ell_1} & \\ & \frac{g}{1+g\ell_2} \end{pmatrix}, \quad (14)$$

which is of course two instances of the single band result. Conversely, when the interband interaction is just as strong as the intraband one, $g_x = g$,

$$\hat{g}_{\text{TAM}}(\omega^*) = \frac{1}{1 + g(\ell_1 + \ell_2)} \hat{g}_{\text{initial}}, \quad (15)$$

i.e., the DOS from *both bands* contributes to the renormalization and suppression of the repulsion – a first hint at the inter-band interactions importance.

Retarded interaction We now introduce the retarded interaction in the Cooper channel. Generally, one may consider two possible scenarios. In the first, the interaction corresponds to an *intraband attraction*, so we define

$$\hat{g} = \hat{g}_{\text{TAM}}(\omega^*) - \begin{pmatrix} g_{\text{intra}} & \\ & g_{\text{intra}} \end{pmatrix}. \quad (16)$$

This is the conventional scenario, to which we refer throughout our calculations. In the second scenario, the retarded interaction scatters Cooper pairs between the bands, and it is necessary to consider *interband repulsion*, i.e.,

$$\hat{g} = \hat{g}_{\text{TAM}}(\omega^*) + \begin{pmatrix} & g_{\text{inter}} \\ g_{\text{inter}} & \end{pmatrix}. \quad (17)$$

We note that in the case of intraband interaction, one must have attraction to have any hope of finding a BCS instability, yet for interband interactions this is not the case. However, as we will demonstrate, *interband repulsion is actually more favorable to superconductivity*. This is because it adds on top of the interband renormalized repulsion u_x , instead of working against it.

Finding T_c Having recovered the interaction matrix \hat{g} , we turn to calculate the susceptibility matrix as a function of temperature,

$$\hat{\chi}(T) = \hat{g}^{-1} + \begin{pmatrix} \mathcal{D}_1(T) & \\ & \mathcal{D}_2(T) \end{pmatrix}, \quad (18)$$

where the electrons inside the ω^* shell contribute the factors (diverging at $T \rightarrow 0$),

$$\mathcal{D}_n(T) = \int_{-\omega^*}^{\omega^*} d\xi \mathcal{N}_n(\xi) \frac{\tanh \frac{\xi}{2T}}{\xi}. \quad (19)$$

The superconducting instability is identified by the singularity of the inverse-susceptibility matrix, i.e.,

$$\det [\hat{\chi}^{-1}(T_c)] = 0. \quad (20)$$

This is a transcendental equation for T_c , which generally has two solutions, of which one must choose the higher T_c , as it marks the superconducting transition.

We may explicitly derive the form of this self-consistent equation for T_c in the two cases discussed above:

1. Intraband attraction –

$$u_x^2 \mathcal{D}_1 \mathcal{D}_2 = [1 - (g_{\text{intra}} - u_1) \mathcal{D}_1] [1 - (g_{\text{intra}} - u_2) \mathcal{D}_2]. \quad (21)$$

2. Interband repulsion –

$$(u_x + g_{\text{inter}})^2 \mathcal{D}_1 \mathcal{D}_2 = [1 + u_1 \mathcal{D}_1] [1 + u_2 \mathcal{D}_2]. \quad (22)$$

The four-fold degenerate case may be of some interest (though irrelevant here considering the experimental data). If $\mathcal{D}_1 = \mathcal{D}_2 \equiv \mathcal{D}$, and $u_1 = u_2 \equiv u$, the equation for T_c looks the same for both cases above, and reads

$$(g_{\text{attraction}} - u + u_x) \mathcal{D} = 1. \quad (23)$$

It is now made even clearer, that in either case the interband interaction u_x always “assists” the retarded pairing glue. It is actually even simpler in the fully degenerate case $\ell_1 = \ell_2 \equiv \ell$,

$$\left(g_{\text{attraction}} - \frac{g - g_x}{1 + (g - g_x) \ell} \right) \mathcal{D} = 1, \quad (24)$$

so T_c is determined by the difference between the bare intraband and intraband repulsion, renormalized by the TAM mechanism.

4 Superconductivity onset dependence on Ising spin-orbit coupling

We consider the main superconducting region across the different devices, referred to as “SC₂”. Consistently, it has been shown by Fermiology measurements that the parent normal-state is mostly two-fold degenerate. In the non-interacting limit, the state is comprised of two spin-valley-locked sectors, the so-called majority and minority bands, split by an energy $\sim 2\lambda_0$. Interactions tend to modify the energy separation, and possibly induce canting, which render the spin-valley locking only approximate.

As the Ising spin-orbit increases and the bands become more separated (interactions only enhance this trend), the high-DOS regions in the two bands move further away from each other, as well. Consequently, it becomes exceedingly difficult to stabilize a regime where the DOS in the vicinity of the Fermi energy is high *in both bands*. A higher displacement field effectively enhances the

high DOS region at energies just below the van-Hove singularity, and thus make this simultaneous-high-DOS regime possible again.

As an illustration of this phenomenon, let us consider the effective Tolmachev-Anderson-Morel pseudo-potential

$$v_{\text{TAM}}^* = \sqrt{\det \hat{g}_{\text{TAM}}(\omega^*)} = \sqrt{\det \left[(\hat{g}_{\text{initial}})^{-1} + \begin{pmatrix} \ell_1 & \\ & \ell_2 \end{pmatrix} \right]^{-1}}. \quad (25)$$

The interaction v_{TAM}^* can easily be verified to give the familiar TAM pseudo-potential in the single band case. Investigating this interaction is motivated by the fact that a superconducting transition is associated with a singularity of the \hat{g} matrix emerging at some energy scale. We point out that this singularity cannot occur without retardation, unless $|g_x| > g$ (this encompasses both attractive interactions $g < 0$, and cases where interband scattering dominates).

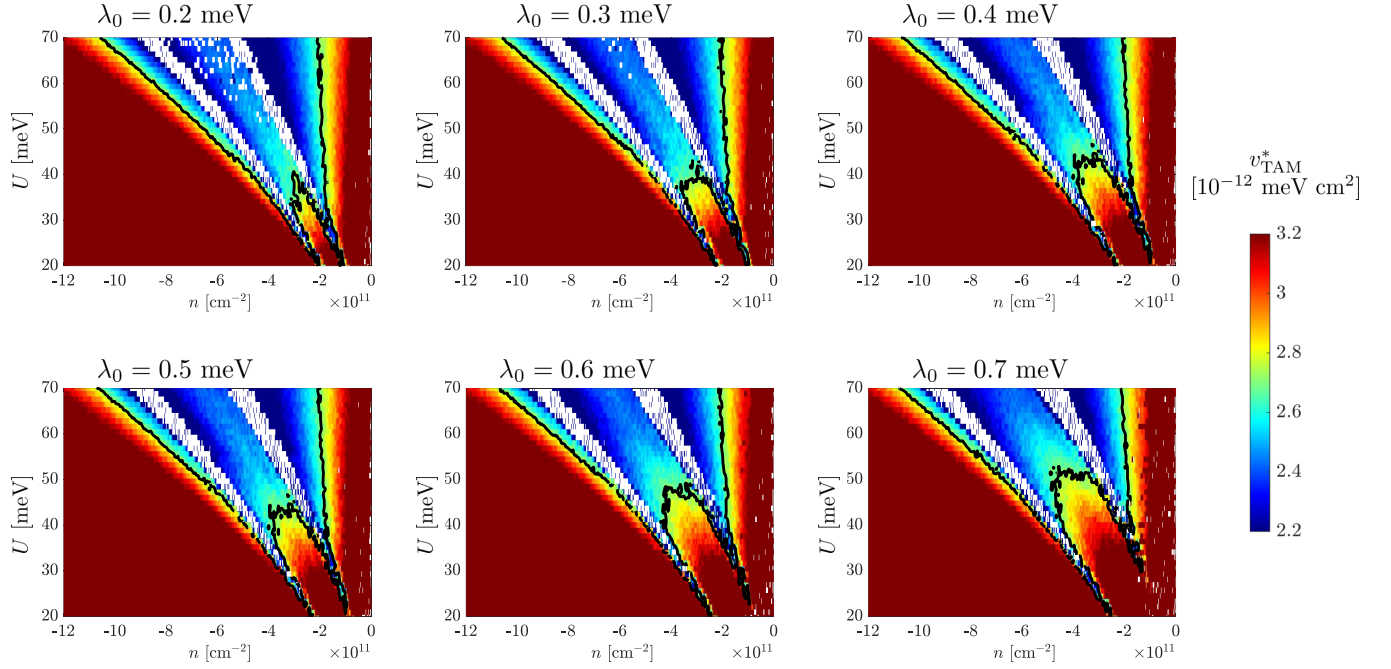
We plot the interaction strength v_{TAM}^* across the phase diagram for different values of the induced ISOC λ_0 in SI Fig. 1. Focusing our attention to within the blank white regions (those indicate where two-fold degeneracy is broken within our simplified analysis), we discover the sought-after trend. Namely, the border of low v_{TAM}^* , and thus superconductivity threshold, moves to higher displacement fields when the ISOC is gradually enhanced. Again, this is due to the interband part of the interaction being most efficient when the DOS near the Fermi level is high in both bands at the same time.

5 Effect of Zeeman magnetic field

Let us discuss how Zeeman coupling of the in-plane magnetic field eventually impacts superconductivity itself.

Intravalley vs. Intervalley interactions Suppose the system we consider is characterized by two interaction scales: low-momentum scattering V_0 , and intervalley scattering V_Q . Originating in Coulomb repulsion, which scales as $1/q$ (q is the magnitude of momentum scattered), one might assume $V_0 \gg V_Q$. This assumption relies on the Fermi momentum, $k_F \sim \sqrt{n}/4 \sim 0.05 \text{ nm}^{-1}$, being much smaller than the intervalley momentum scale, $Q \approx 17 \text{ nm}^{-1}$. However, as was similarly argued in Refs. 57, 59, 60, k_F is not the relevant momentum here, as significant Thomas-Fermi screening takes place. The Thomas-Fermi momentum, $q_{TF} = 2\pi e^2 \mathcal{N}(\bar{\mu}) / \epsilon_r$ is of order $\mathcal{O}(10 \text{ nm}^{-1})$ (considering $\epsilon_r = 4$ for hBN and the relevant density ranges). It is thus entirely possible that V_0 and V_Q are comparable in strength, and both are of the order of magnitude of the inverse DOS at the Fermi level (as the Thomas-Fermi approximation suggests).

Considering the two bands or sectors are separated by spin-valley locking (mostly due to the in-



Supplementary Information Fig. 1 | ISOC dependence of the residual Coulomb repulsion v_{TAM}^* . Different panels correspond to calculations of Eq. (25) in the presence of different ISOC values, indicated on top of each panel. The first and last panels correspond to Fig. 21 in the main text. Note that the Ising splitting referred to in the main text is $\lambda_I = 2\lambda_0$, where λ_0 enters the model via Eq. (5). For emphasis, the black contour line marks the value $v_{\text{TAM}}^* = 2.7 \times 10^{-12}$ meV cm². The blank white regions mark areas where the system develops valley-polarization, and superconductivity is thus suppressed. Here, we use the Thomas-Fermi screening approximation, where $g \approx \mathcal{N}_{\text{tot.}}(E_F)$, the total Fermi-level DOS, and $g_x = 0.5g$. Other parameters used in this plot: $\omega^* = 0.35$ meV, $U_C = 1.4$ eV nm², $J = U_V = 0.2$ eV nm².

duced Ising spin-orbit coupling), one identifies

$$g = V_0, \quad g_x = V_Q, \quad (26)$$

where we have assumed the scattering interactions preserve spin. However, if everything is kept the same, but now a canting angle $\theta \in [0, \frac{\pi}{2}]$ is introduced, such that $\theta = 0$ corresponds to the spin-valley locked phase, and $\theta = \pi/2$ corresponds to two sectors with completely opposite spin polarization within the plane, one finds

$$g = V_0 + V_Q \sin^2 \theta, \quad g_x = V_Q (1 - \sin^2 \theta). \quad (27)$$

Notice that for complete polarization g_x vanishes – this process now flips two spins and cannot be facilitated by the Coulomb interactions. Through this relation, and the self-consistent equation for superconducting T_c , *superconductivity becomes directly impacted by the canting angle*. Importantly, no pair-breaking within the different sectors occurs, and the Zeeman effect (which we will now demonstrate) only acts as a knob on the Cooper channel interaction strength.

Canting due to Zeeman in the presence of interactions Consider the mean-field free energy of a two-fold symmetric phase, with order parameter δn , in the presence of short-range repulsion U_C , ferromagnetic Hund's coupling J , and in-plane Zeeman energy V_Z ,

$$\begin{aligned} F(\delta n, \phi; n) = & 2E_{\text{kin}}\left(\frac{n + \delta n}{4}; \frac{n}{4}\right) + 2E_{\text{kin}}\left(\frac{n - \delta n}{4}; \frac{n}{4}\right) - \frac{U_C}{8}\delta n^2 \\ & - \lambda_0 s_z \tau_z - J \mathbf{S}_+ \cdot \mathbf{S}_- - V_Z S_x, \end{aligned} \quad (28)$$

where $E_{\text{kin}}(n_1; n_2)$ is the kinetic energy associated with maintaining the density n_1 instead of the paramagnetic density n_2 . In terms of the sector imbalance δn and canting angle θ , the magnetic part of the free energy is

$$\frac{F_{\text{mag}}}{\delta n} = -\lambda_0 \cos \theta + \frac{J\delta n}{4} \cos 2\theta - V_Z \sin \theta. \quad (29)$$

Let us approximate the dependence on δn and the canting angle θ as being roughly separable. In that case, we may minimize F_{mag} with respect to θ independently, arriving at the following transcendental equation for extracting θ ,

$$\lambda_0 \tan \theta - J\delta n \sin \theta = V_Z. \quad (30)$$

Notice that for $V_Z = 0$, one obtains $\theta = \cos^{-1} \frac{\min\{\lambda_0, J\delta n\}}{J\delta n}$, and one obtains full spin polarization ($\theta = \pi/2$) in the absence of spin-orbit coupling, as expected. Importantly, Eq. (30) clearly indicates the role of the majority-minority imbalance δn in determining the canting angle, as well as its susceptibility to a Zeeman term.

Comparison of different superconducting regions The mechanism described in detail above sheds light on the differing behaviors of various superconducting domes when subjected to an in-plane magnetic field.

The particularly relevant regions, considering the flavor occupation picture revealed by quantum oscillations, are SC_1 and the higher-hole-density part of SC_2 (the main dome). These two superconductors fit nicely within our framework of interband superconductivity, as they are comprised of two bands, minority and majority, each doubly degenerate. However, they have one important differentiating feature: the relevant interband polarization δn is significantly larger for SC_2 . The difference can already be gleaned from the experimental data, see Fig. 3c of the main text, where the quantum-oscillations feature corresponding to the majority band drops abruptly in the SC_1 region. This indicates a much smaller δn . The difference in δn is also readily apparent in our variational Hartree-Fock calculation, SI Fig. 2a, where it can be traced to the different DOS in the appropriate filling range.

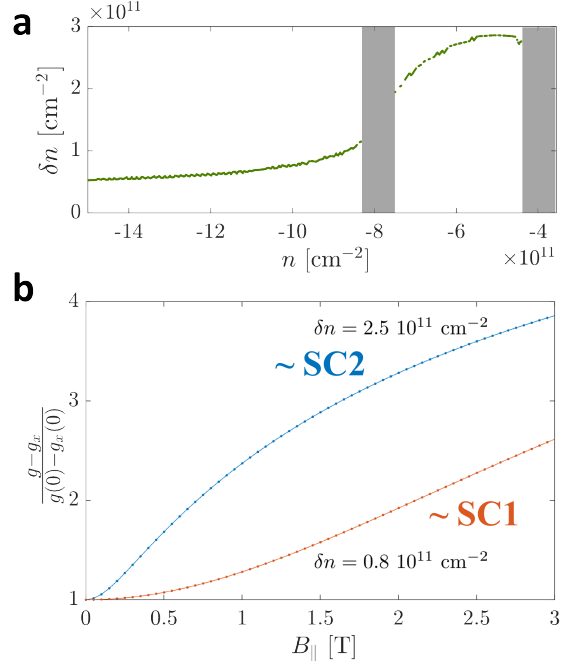
As such, we would expect [given Eqs. (30) and (27)] SC_2 to be much more sensitive to the in-plane field as compared to SC_1 . In SI Fig. 2b, we compare the relative strength of intraband and interband interactions as a function of magnetic field, for two representative values of δn . The canting angle is extracted via Eq. (30). As expected, the interactions corresponding to SC_2 are much more sensitive to the in-plane field. This is in complete agreement with the experimental data, as the Pauli-limit violation ratio (PVR) for SC_1 is ~ 18 , whereas for SC_2 it is noticeably lower, $PVR \sim 4$.

Remarkably, the trend in T_c in this part of SC_2 is well captured by our model calculations. For a large portion of this region, the critical temperature at small magnetic fields largely follows the relation

$$T_c(B_{\parallel}) - T_c(0) \approx -\alpha B_{\parallel}^2. \quad (31)$$

For example, in the data presented in Fig. 4 in the main text, the experimental value remains roughly constant in the left (lower density) part of the SC_2 dome, with $\alpha \approx 0.08$ Kelvin/Tesla². Our calculations, taking into account the magnetic field effects discussed in this section, are in good agreement both with the B_{\parallel}^2 trend, and with the numerical value of the prefactor α . This is demonstrated in SI Fig. 3, where the T_c behavior follows almost perfectly the behavior in Eq. (31) with the approximate experimental value.

To perform these calculations, we take as phenomenological input the shape of the Fermi surfaces observed in quantum oscillations. For the majority bands we take density per flavor in the range $[-3.85, -3.35] 10^{11} \text{ cm}^{-2}$, and for the minority bands $[-1.35, -1.25] 10^{11} \text{ cm}^{-2}$. Moreover, to account for the fact that the minority bands consist of two small pockets (instead of the expected three



Supplementary Information Fig. 2 | Understanding the discrepancy of in-plane magnetic field sensitivity between SC₁ and SC₂. **a**, Majority-minority band population imbalance δn as a function of density. Here we used $D = 0.8$ V/nm, and $\lambda_0 = 0.6$ meV. Gray rectangles mark regions where the two-fold degeneracy is broken within our variational Hartree-Fock analysis. The parameters we use to extract the normal state properties are identical to those in SI Fig. 1. **b**, Relative difference between the intraband (g) and interband g_x interactions as a function of magnetic field. We plot the trend for two representative values of δn (indicated in the panel), appropriate for the SC₁ (orange) and SC₂ regions. It is clear that repulsion grows more rapidly with magnetic field in the SC₂ region, alluding to the enhanced sensitivity of the corresponding superconductor. Here, $V_0 = 3.1$ eV nm², $V_Q = 2.2$ eV nm².

due to trigonal warping), we introduce a nematic order parameter which breaks the C_3 symmetry,

$$h_\tau(\mathbf{k}) \rightarrow h_\tau(\mathbf{k}) + \begin{pmatrix} & \Delta_{\text{nem}} \\ \Delta_{\text{nem}} & \end{pmatrix}, \quad (32)$$

and we used $\Delta_{\text{nem}} = -15$ meV to match the experimental observation in the desired density range. Other parameters used: $\omega^* = 0.8$ meV, $V_0 = 3.1$ eV nm², $V_Q = 2.2$ eV nm², $J = 0.1$ eV nm², $g_{\text{attraction}} = 0.38$ eV nm², $\lambda_0 = 0.6$ meV.

Conversely, there is a marked change in behavior of SC₂ when moving closer to the charge neutrality point. Namely, T_c becomes much less sensitive to magnetic fields and the magnitude of the corresponding α prefactor becomes much smaller. Again, the quantum oscillation data provides us with important information. The data is consistent with flavor polarization developing within the minority bands themselves. Such polarization can be characterized by an order parameter $\delta n_{\text{minority}}$, such that in the absence of polarization $\delta n_{\text{minority}} = 0$, and when only one flavor (of the two minority ones) is occupied $\delta n_{\text{minority}} = n_{\text{minority}}$. Under the reasonable assumption of zero-momentum Cooper pairing, and considering the fact that the newly polarized flavors correspond to opposite valleys, one expects the minority bands to gradually decouple from the Cooper channel as this polarization increases.

To concretely illustrate this effect, we extract the appropriate Fermi energies in the minority sector, which correspond to a given $\delta n_{\text{minority}}$,

$$2 \int_0^{E_+} d\epsilon \mathcal{N}_2(\epsilon) = n_{\text{minority}} + \delta n_{\text{minority}}, \quad 2 \int_0^{E_-} d\epsilon \mathcal{N}_2(\epsilon) = n_{\text{minority}} - \delta n_{\text{minority}}. \quad (33)$$

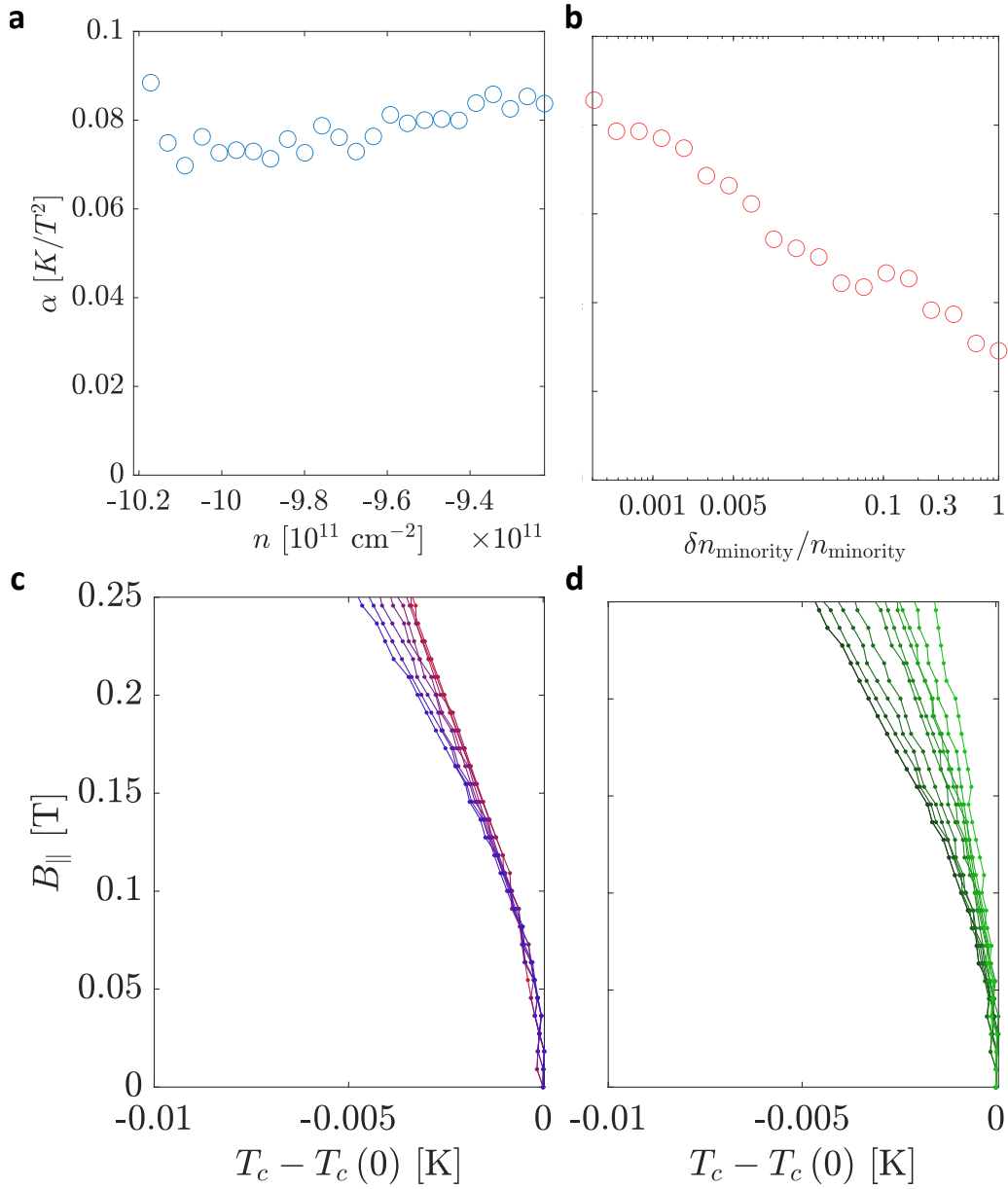
Taking $E_0 = E_\pm$ ($\delta n_{\text{minority}} = 0$), we define $\xi_\pm = E_\pm - E_0$. Thus, in the presence of this secondary polarization the appropriate Cooper integrals in the minority sector are altered,

$$\ell_2 = \left\{ \int_{\max\{\omega^*, \xi_+\}}^\infty + \int_{-\infty}^{\min\{-\omega^*, \xi_-\}} \right\} d\xi \frac{\mathcal{N}_2(\xi)}{|\xi|}, \quad (34)$$

$$\mathcal{D}_2 = \left\{ \int_{\xi_+}^{\max\{\omega^*, \xi_+\}} + \int_{\min\{-\omega^*, \xi_-\}}^{\xi_-} \right\} d\xi \mathcal{N}_2(\xi) \frac{\tanh \frac{\xi}{2T}}{\xi}. \quad (35)$$

We have implicitly assumed here that the relevant temperature regime, i.e., the vicinity of T_c , is much smaller than ξ_\pm/k_B . Notice that in the absence of polarization $\xi_+ = \xi_- = 0$, and we recover the previous expressions.

As we show in SI Fig. 3, we indeed recover the experimental trend. The underlying reason is that the magnetic field behavior we consider relates solely to the interband interactions in the Cooper



Supplementary Information Fig. 3 | In-plane field dependence of superconductivity in the SC_2 dome. **a**, The coefficient α extracted for a range of densities corresponding to the lower density region of SC_2 , featuring an approximately constant coefficient. **b**, At the highest density of panel **a**, we introduce a polarization within the minority sector. The polarization gradually decouples the minority band from the Cooper channel, making the superconductor less sensitive to the magnetic field. **c,d**, Representative plots used to extract the fit parameter α in panels **a,b**, respectively. Details regarding the methodology and precise parameters used in the calculations can be found in the text of Sec. 5.

channel between majority and minority bands. Once one of these sectors stops “pulling its own weight”, eventually only an effective single-band (only majority) superconductor remains, and the magnetic field may only impact it through other effects we do not consider, e.g., an orbital effect (See also discussion of Sec. 6).

In this context, it is worth mentioning that in the normal state of SC_3 the quantum oscillation data is consistent with single band superconductivity, with significant time-reversal symmetry breaking in at least one of the sectors. As a result, our analysis would suggest reduced sensitivity to the B_{\parallel} for the same reason we just discussed. Remarkably, it appears indeed that SC_3 is the superconducting pocket which is most robust in the presence of the magnetic field, and has by far the largest Pauli limit violation in the measured devices.

In summary, the behavior of the different superconducting pockets as a response to an in-plane magnetic field strongly suggests that *interband interactions in the Cooper channel play a crucial role in BLG superconductivity*. Recognizing this prominent role, we may comment on the disparity between superconductivity in BLG with or without WSe_2 . Namely, in the former superconductivity is much stronger and more robust than the latter. In the two-fold polarized regime (majority and minority sectors are well separated in energy), the system is spin-polarized without WSe_2 due to intervalley Hund’s coupling. Thus, interband interactions are entirely absent in the Cooper channel due to spin conservation. Introduction of Ising spin orbit coupling “re-shuffles” the polarization cascade, and favors spin-valley locking as the two-fold phase even at moderate values of the induced spin orbit coupling. This “shifts” interaction strength from the intraband part of the coupling matrix to the interband part, Eq. (27). As we have demonstrated above, such a shift towards stronger interband interactions may have a *great positive impact on superconductivity*.

6 Analysis of SOC, orbital and Zeeman depairing mechanisms

We now discuss SOC, orbital, and Zeeman depairing mechanisms in Ising superconductors. We follow the treatment first developed in Ref. 51 to compute the response to a Zeeman field of non-centrosymmetric superconductors with Rashba SOC, later generalized in Refs. 52, 53 to systems with a coexistence of Ising and Rashba SOC. Parts of the discussion present in this supplement mirror our earlier analysis of Ref. 17. The analysis of this section complements the previous section, intending to provide contrast and further strengthen the interpretation above. Namely, the trends observed in the experiment as a function of in-plane magnetic field likely points to the prominence of majority-minority interband interactions.

We assume that as a result of flavor symmetry-breaking transition (cascade), the carriers in the parent states of SC_1 , SC_2 , and SC_3 occupy the relevant number of trigonal-warping pockets as discussed in the main text. Each trigonal-warping pocket we model as two electronic bands centered around trigonal-warping loci \mathbf{T} that respectively originate from the K and K' valleys. We also assume that the selected pockets in the two valleys are time-reversed partners of each other to

allow for the formation of zero-momentum pairing naturally.

As mentioned in the text, we stress that the quantum oscillation data do not directly reveal nematicity but rather only inform about the number and relative sizes of Fermi pockets. If the Fermi pockets are not the trigonal warping pockets but rather some other Fermi pockets resulting from the interaction-driven reconstruction of the electronic spectrum, then the following modeling could still apply, provided that time reversal symmetry \mathcal{T} , which relates the two remaining small pockets is preserved. The specific relation between the effective Ising, Rashba, and orbital coupling, however, in such a case, would not be related to the microscopic parameters of the continuum model that we will derive in the following subsection.

Effective Hamiltonian in the trigonal warping pockets Here we derive an effective low-energy 2×2 Hamiltonian describing two SOC split bands at each trigonal warping loci. This Hamiltonian serves as a starting point for the following analysis as it allows us to connect microscopic model parameters (Ising, Rashba, Orbital, displacement field) with the low-energy theory. The purpose of this exercise is to provide analytic intuition about what energy and momentum scales in the problem control the depairing. Moreover, this procedure allows us to reduce the number of fitting parameters to just Rashba coupling as Ising SOC is determined experimentally, and orbital coupling is a property of the system.

The starting point of our analysis is the valley-dependent ($\tau = \pm 1$) Hamiltonian in spin, layer, and sublattice basis:

$$h_{full,\tau} = h_{0,\tau} + h_{I,\tau} + h_{R,\tau} + h_{orb,\tau} + h_Z, \quad (36)$$

where $h_{0,\tau} = s_0 \otimes h_\tau$ with h_τ given by Eq. (2) (we set $\Delta' = 0$ for simplicity) and describes the non-interacting Hamiltonian of bilayer graphene in the absence of SOC and magnetic field. We use the shorthand notation, s_0, s_x, s_y, s_z , for Pauli matrices in the spin space. The other entries in the above expression correspond to Ising SOC ($h_{I,\tau}$), Rashba SOC ($h_{R,\tau}$), orbital coupling ($h_{orb,\tau}$),

and Zeeman energy (h_Z). They are given by:

$$h_{I,\tau} = \frac{1}{2}\tau\lambda_I \left[s_z \otimes \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \end{pmatrix} \right] \quad (37)$$

$$h_{R,\tau} = \frac{1}{2}\lambda_R \left[\tau s_y \otimes \begin{pmatrix} 0 & 1 & 0 & 0 \\ 1 & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \end{pmatrix} - s_x \otimes \begin{pmatrix} 0 & -i & 0 & 0 \\ i & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \end{pmatrix} \right] \quad (38)$$

$$h_Z = \mu_B B \left[(\cos\theta_B s_x + \sin\theta_B s_y) \otimes \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 1 & 0 \\ 0 & 0 & 0 & 1 \end{pmatrix} \right] \quad (39)$$

$$h_{orb,\tau} = \lambda_{orb} \left[\tau \sin\theta_B s_0 \otimes \begin{pmatrix} 0 & -1 & 0 & 0 \\ -1 & 0 & 0 & 0 \\ 0 & 0 & 0 & 1 \\ 0 & 0 & 1 & 0 \end{pmatrix} + \cos\theta_B \otimes \begin{pmatrix} 0 & -i & 0 & 0 \\ i & 0 & 0 & 0 \\ 0 & 0 & 0 & i \\ 0 & 0 & -i & 0 \end{pmatrix} \right] \quad (40)$$

In the above expressions, we explicitly write the sublattice and layer structure of the matrices to highlight that the Ising and Rashba SOC are induced only on one layer, which is in proximity to the TMD. The angle θ_B determines the direction of the in-plane magnetic field B with $\theta_B = 0$ corresponding to the x-direction in the continuum model. The orbital coupling enters via minimal coupling (See Ref.61 for derivation). Its magnitude (See also Ref. 17):

$$\lambda_{orb} = \frac{v_0 e d}{2\hbar} = \frac{\sqrt{3}\gamma_0 a_0 e d}{4\hbar} \approx 0.14 \frac{\text{meV}}{\text{Tesla}}. \quad (41)$$

yields a stronger coupling than the spin Zeeman term h_Z with the Bohr magneton $\mu_B \sim 0.06$ meV/Tesla hinting at the role of orbital coupling in depairing. In the above Hamiltonian, in principle, all parameters are known or determined via experiment except λ_R .

We now follow the standard perturbation theory approach discussed, for example, in Ref. 37,62 to arrive at a low-energy theory description of the trigonal warping pockets. The difference in our analysis compared to that of Ref. 37,62 is that we keep both the trigonal warping term, v_3 , which is necessary to account for the three pockets as well as the displacement field U necessary to polarize charges to one side. Details and further discussion of the calculation are provided in Ref. 63. Carrying out the analysis, we arrive at an effective Hamiltonian $h_{eff,\tau}$ in each trigonal warping pocket (in the spin up and down basis):

$$h_{eff,\tau} = \tilde{h}_{0,\tau} + \tilde{h}_{I,\tau} + \tilde{h}_{R,\tau} + \tilde{h}_{orb,\tau} + \tilde{h}_Z, \quad (42)$$

where the individual terms are:

$$\tilde{h}_{0,\tau} \approx \epsilon^0(\mathbf{p})s_0 \quad (43)$$

$$\tilde{h}_{I,\tau} \approx \frac{1}{2}\tau\lambda_I s_z \quad (44)$$

$$\tilde{h}_{orb,\tau} \approx g_{orb}(\mathbf{p})s_0 \quad (45)$$

$$\tilde{h}_{R,\tau} \approx \frac{1}{2}(g_{R,x}(\mathbf{p})s_y - g_{R,y}(\mathbf{p})s_x) \quad (46)$$

$$\tilde{h}_Z \approx \mu_B B (\cos \theta_B s_x + \sin \theta_B s_y) . \quad (47)$$

Here we expanded around a trigonal warping center located along the x -axis focusing on leading order terms where $\gamma_0(v)$ and γ_1 were the large energy scales in the problem (Analogously to Ref. 37, 62). The dispersion of other pockets can be analogously derived by the rotating location of the T . Momentum \mathbf{p} is measured with respect to the trigonal warping pocket center $T = T\hat{x}$:

$$T = \frac{\sqrt{\gamma_1^2 v_3^2 + 4U^2 v^2} + 3\gamma_1 v_3}{4v^2} \quad (48)$$

The parameters γ_1, v_3, v are the continuum model parameters defined in Eq. (2). U is the applied displacement field in units of energy difference across layers. As the displacement field grows, the trigonal warping centers move away from the K, K' points with Uv comparable to $\gamma_1 v_3$ for the relevant U for the experiment.

In the above equation the effective orbital coupling scale g_{orb} is

$$g_{orb} \approx \lambda_{orb} \frac{Uv(p_y \cos \theta_B - (\tau T + p_x) \sin \theta_B)}{\gamma_1^2} . \quad (49)$$

We see that as U increases, the role of orbital coupling becomes more pronounced. We also see that the effective orbital coupling has two characteristic momentum scales: (i) one sensitive to the filling of the small pockets (i.e., momentum \mathbf{p} dependent) and (ii) one set by the location of the trigonal warping pocket T . Depending on the orientation of the magnetic field (θ_B), the effective orbital coupling can change drastically, hinting at a potential sensitivity to in-plane field orientation.

Lastly the effective Rashba couplings $g_{R,x}(\mathbf{p})$ and $g_{R,y}(\mathbf{p})$ are given by:

$$g_{R,x}(\mathbf{p}) \approx \lambda_R \frac{p_y v (14\gamma_1 T v_3 + U^2)}{4\gamma_1^2 U} \quad (50)$$

$$g_{R,y}(\mathbf{p}) \approx \lambda_R \left[\frac{\tau T U v}{4\gamma_1^2} + \frac{p_x v (10\gamma_1 T v_3 + 3U^2)}{4\gamma_1^2 U} \right] . \quad (51)$$

Just as in the case of the effective orbital coupling, we find that there are two contributions to the effective Rashba coupling: (i) one set by the location of the trigonal warping pocket T and (ii) one

controlled by the doping of each pocket and hence momentum p_x, p_y . Physically, the two origins of the terms make sense: (i) controls the winding of the Rashba spin texture around the K, K' points, and (ii) controls the winding of the Rashba spin texture around the trigonal warping center. In the above expression, we focused on the leading order terms for typical numerical values (See Ref. 63 for further discussion).

Crucially, from the above result, we find that the effective Ising in each trigonal pocket is, to leading order, unmodified from the microscopic Ising value by the projection to each pocket. However, the effective orbital and Rashba contributions are different. Both orbital and Rashba contributions feature dependence on two characteristic momenta: (i) momentum location of the trigonal warping pocket from the K, K' (which is displacement field (U) dependent) and (ii) a momentum p measured with respect to each pocket center. Both terms are significant in determining the magnitude of the effective orbital and Rashba parameters.

Depairing analysis for $\lambda_I \ll E_F$ We now proceed to analyze the depairing mechanisms using the practical model of Eq. (42) as the normal state Hamiltonian. As mentioned before, we will follow the treatment first developed in Ref. 51 to compute the response to a Zeeman field of non-centrosymmetric superconductors with Rashba SOC, later generalized in Refs. 52, 53 to systems with a coexistence of Ising and Rashba SOC. The approach mirrors that carried out by us in Ref. 17, however here we focus on analytical understanding of the $T_C \rightarrow T_{C,0}$ limit (here $T_{C,0}$ is the depairing temperature in the absence of in-plane field). We will also use the results of the previous subsection to constrain the estimates with realistic microscopic parameters.

To connect to the previous work of Ref. 17, we further rewrite the normal-state Hamiltonian as

$$h_{eff,\tau}(\mathbf{p}) = \xi(\mathbf{p}) + \frac{1}{2}\tau\lambda_I s^z + \frac{1}{2}(\mathbf{s} \times \mathbf{g}_R(\mathbf{p})) \cdot \mathbf{z} + \mathbf{b} \cdot \mathbf{s} + (\mathbf{b} \times \mathbf{g}_{orb}(\mathbf{p})) \cdot \mathbf{z}, \quad (52)$$

On the right side $\xi(\mathbf{k})$ is the spin-orbit-free normal state band structure, which we linearize near the Fermi surface as $\xi(\mathbf{k}) \approx v_F(p - p_F)$ (p_F denotes the Fermi momentum measured from the center \mathbf{T} of the pocket). The next two terms incorporate Ising and Rashba SOC. Although the Rashba SOC, when projected to the trigonal warping pocket, is not isotropic with respect to the pocket center (as the pocket is not isotropic either), see Eq. (46), for simplicity of the analysis, we will approximate the Rashba as

$$\mathbf{g}_R(\mathbf{p}) \approx g_{R,0} + g_{R,1}(p_y, p_x) \quad g_{R,0} = \lambda_R \frac{\tau T U v}{4\gamma_1^2} \quad g_{R,1} = \lambda_R \frac{v(10\gamma_1 T v_3 + 3U^2)}{4\gamma_1^2 U}. \quad (53)$$

By comparison with Eq.(46), this overestimates the Rashba coupling, but for the purpose of this analysis, it is sufficient. For the orbital coupling, we focus on the in-plane field oriented along x -axis (we leave the discussion of in-plane direction dependence to the next section), giving

$$\mathbf{g}_{orb}(\mathbf{p}) = \lambda_{orb} \frac{U v p_y}{\gamma_1^2} (0, 1) \quad (54)$$

The term $\mathbf{b} \cdot \mathbf{s}$ is simply the Zeeman energy, which for an in-plane magnetic field B along x -axis takes the form $\mathbf{b} = (\mu_B B, 0, 0)$ with μ_B the Bohr magneton. We pause here to highlight that unlike the analysis of Ref. 17, here, in principle, there is only one undermined parameter λ_R with the remainder of the Hamiltonian known.

To analyze depairing, we then consider a local (momentum-independent) spin-singlet pairing term that gives rise to superconductivity with a critical temperature T_c^0 at zero magnetic field. In the presence of an in-plane magnetic field B , the superconductivity is weakened through a combination of spin and orbital effects, with $T_c < T_c^0$ given by the solution of a self-consistent gap equation linearized near the second-order transition at T_c where the pairing amplitude $\Delta \rightarrow 0$,^{51-53,64,65}

$$\ln \left(\frac{T_c}{T_c^0} \right) = \frac{T_c}{2} \sum_{\omega_n} \left(\left\langle \int d\xi_{\mathbf{p}} \text{Tr} \{ s_y G_{0,\tau}(\mathbf{p}, i\omega_n) s_y G_{0,-\tau}^*(-\mathbf{k}, i\omega_n) \} \right\rangle_{\text{FS}} - \frac{\pi}{|\omega_n|} \right). \quad (55)$$

Here \sum_{ω_n} denotes a summation over Matsubara frequencies $i\omega_n$, $\langle \dots \rangle_{\text{FS}}$ denotes a Fermi surface average and $\text{Tr}\{\dots\}$ is a trace over spin Pauli matrices, and $G_{0,\tau}(\mathbf{p}, i\omega_n)$ is the normal-state Green's function given of the Hamiltonian from Eq.(52). The above equation can be further simplified (as done previously and in literature⁵¹⁻⁵³) to yield a non-linear equation connecting critical depairing magnetic field with the relevant temperature T_C . The pairing glue strength is parametrized here by the $T_{C,0}$ - the temperature without a magnetic field. We also note that in arriving at the above equation, we used the condition that chemical potential E_F is larger than any SOC scale. Thus, we also allow for an interband pairing in the above expression, however the pairing glue is not renormalized as discussed in the mechanism from the previous section. In the next subsection, we focus on the other limit of $E_F \ll \lambda_I$.

To make an explicit connection to the experimental fitting of $T_C = T_{C,0} - \alpha B^2$, we focus on the $T_C \rightarrow T_{C,0}$ limit of Eq.(55). In such cases, we can arrive at (See Ref. 63 for further discussion and details of the derivation) at a microscopic expression for α

$$\alpha = \alpha_0 + \alpha_{orb} \quad (56)$$

$$\alpha_0 \approx T_{C,0} \mu_B^2 \frac{2\lambda_I^2 + \tilde{g}_R^2}{(\lambda_I^2 + \tilde{g}_R^2)^2} \Phi(\rho) + \frac{\alpha_C \mu_B^2}{2k_B^2 T_{c0}} \frac{\tilde{g}_R^2}{\lambda_I^2 + \tilde{g}_R^2} \quad (57)$$

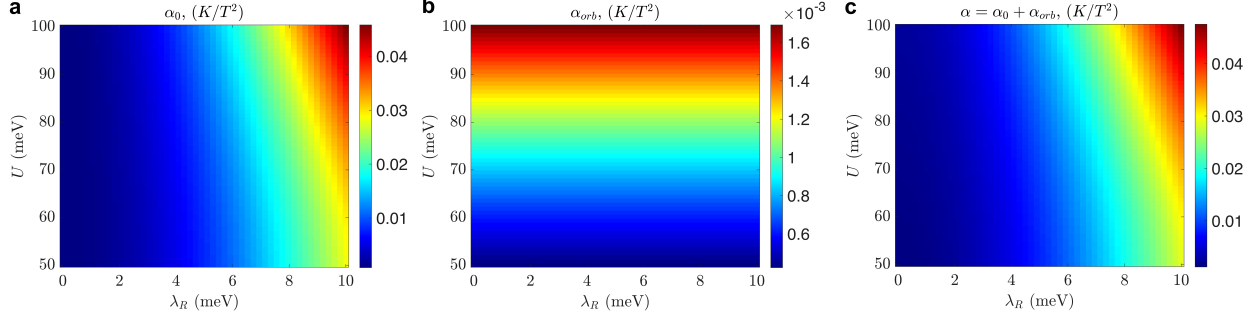
$$\alpha_{orb} \approx \alpha_C \frac{\tilde{g}_{orb}^2}{k_B^2 T_{c0}}, \quad \alpha_C = \frac{\Psi''(1/2)}{8\pi^2} \quad (58)$$

where we separated α into two parts orbital independent (α_0) and orbital dependent part(α_{orb}). Here, the effective Fermi surface averaged Rashba and orbital couplings are given by:

$$\tilde{g}_{orb} \approx \lambda_{orb} \frac{U v p_F}{\gamma_1^2}, \quad \tilde{g}_R \approx \lambda_R \frac{\tau T U v}{4\gamma_1^2} + \lambda_R \frac{v(10\gamma_1 T v_3 + 3U^2)}{4\gamma_1^2 U} p_F. \quad (59)$$

The special functions are defined as

$$\Phi(\rho) \equiv \frac{1}{2} \{ \text{Re} \left[\Psi \left(\frac{1+i\rho}{2} \right) - \Psi \left(\frac{1}{2} \right) \right] \}, \quad \rho = \frac{\sqrt{\lambda_I^2 + \tilde{g}_R^2}}{\pi k_B T_{C,0}} \quad (60)$$



Supplementary Information Fig. 4 | Coefficient α in $T_C = T_{C,0} - \alpha B^2$ in the $E_F \gg \lambda_I$ limit. Dependence of the coefficients α_0 (a), α_{orb} (b), and $\alpha = \alpha_0 + \alpha_{orb}$ (c) from Eq.(56) on layer potential U and Rashba coupling λ_R . Here we use $p_F \sim \sqrt{n}/4 \sim 0.05 \text{ nm}^{-1}$ at $T_{C,0} \approx 100 \text{ mK}$ and $\lambda_I = 1.5 \text{ meV}$.

and $\Psi(z)$, $\Psi''(z)$ is the DiGamma function and its second order derivative.

Let us now analyze the consequences of the result in Eq.(56). As expected, when Ising SOC increases, α decreases, in line with the expected Ising superconductor behavior (i.e., superconductor becomes more resilient to depairing). Rashba SOC and orbital coupling contribute to depairing, with the contributions being additive. SI Fig. 4a-c shows plots of the two parts of the α coefficient separately (SI Fig. 4a,b) and combined (SI Fig. 4c) as a function of layer potential U and microscopic λ_R for $p_F \sim \sqrt{n}/4 \sim 0.05 \text{ nm}^{-1}$ at $T_{C,0} \approx 100 \text{ mK}$ and $\lambda_I = 1.5 \text{ meV}$. We find that no realistic value of $\lambda_R < 10 \text{ meV}$ reproduces the experimental values of $\alpha \sim 0.1 \text{ K/T}^2$ seen in SC_2 (we are about an order of magnitude too small). This conclusion also holds if the direction of the B_{\parallel} were rotated to increase the orbital coupling, c.f. Eq.(49). For the SC_1 case however where the superconductor is more robust to depairing with the experimental $\alpha \lesssim 0.01 \text{ K/T}^2$ the theoretically predicted α is in agreement for reasonable $\lambda_R < 2 \text{ meV}$ values.

To phrase it differently, using realistic microscopic SOC and orbital coupling values is insufficient to account for the suppression of superconductivity with an in-plane field in the SC_2 phase. This apparent robustness is a consequence of approximating the intra and interband pairing as having constant magnitude. As argued in Sec. 5, however, the interband and intraband interactions are modified in the presence of a magnetic field due to canting effects, thus reducing the robustness to the in-plane field and increasing α .

Depairing analysis for $\lambda_I \gg E_F$ In the analysis of the previous section, we were working in the conventional limit used for the Ising superconductors of E_F being the largest energy scale in the problem. As a result, the microscopic dispersion dependence ξ_p effectively dropped out of the calculation. However, given that in the large U limit, the trigonal warping pockets become flat promoting interactions, it is also insightful to consider the other limit of $\lambda_I \gg E_F$. In this limit, we will focus solely on an intraband pairing between the small trigonal warping pockets (the minority carriers) in each valley, as the interband pairing should be subleading.

We begin by writing the linearized intraband gap equation for the pairing temperature

$$\frac{2}{g} = \int \frac{d^2\mathbf{p}}{(2\pi)^2} \frac{\tanh\left(\frac{\epsilon_{\tau,\mathbf{p}}}{2k_B T_C}\right) + \tanh\left(\frac{\epsilon_{-\tau,-\mathbf{p}}}{2k_B T_C}\right)}{\epsilon_{\tau,\mathbf{p}} + \epsilon_{-\tau,-\mathbf{p}}}, \quad (61)$$

where $\epsilon_{\tau,\mathbf{p}} = \epsilon_{\tau,\mathbf{p}}^0 + s_{\tau,\mathbf{p}}$ is the dispersion of carriers. Here $\epsilon_{\tau,\mathbf{p}}^0$ is the dispersion of the carriers in the absence of SOC and magnetic field (See Eq.(42)) and the $s_{\tau,\mathbf{p}}$ is the SOC, orbital and Zeeman field dependent part. Crucially $\epsilon_{\tau,\mathbf{p}}^0 = \epsilon_{-\tau,-\mathbf{p}}^0$, but $s_{\tau,\mathbf{p}} \neq s_{-\tau,-\mathbf{p}}$ giving rise to depairing.

To eliminate the pairing constant g we can use the analogous $T_{C,0}$ expression

$$\frac{2}{g} = \int \frac{d^2\mathbf{p}}{(2\pi)^2} \frac{\tanh\left(\frac{\tilde{\epsilon}_{\tau,\mathbf{p}}}{2k_B T_{C,0}}\right) + \tanh\left(\frac{\tilde{\epsilon}_{-\tau,-\mathbf{p}}}{2k_B T_{C,0}}\right)}{\tilde{\epsilon}_{\tau,\mathbf{p}} + \tilde{\epsilon}_{-\tau,-\mathbf{p}}}, \quad (62)$$

where $\tilde{\epsilon}_{-\tau,-\mathbf{p}}$ is the dispersion $\epsilon_{\tau,\mathbf{p}} = \epsilon_{\tau,\mathbf{p}}^0 + s_{\tau,\mathbf{p}}$ evaluated at $B \rightarrow 0$. Using Eq.(61) and Eq.(62), eliminated g and expanding near $T_C \rightarrow T_{C,0}$ we arrive at the desired form

$$T_C = T_{C,0} - \alpha B^2, \quad (63)$$

where

$$\alpha \approx T_{C,0} \frac{F}{G}, \quad G \approx \int \frac{d^2\mathbf{p}}{(2\pi)^2} \frac{1}{2k_B T_{C,0}} \text{sech}^2\left(\frac{2\epsilon_{+,\mathbf{p}}^0 + \lambda_I}{4k_B T_{C,0}}\right) \quad (64)$$

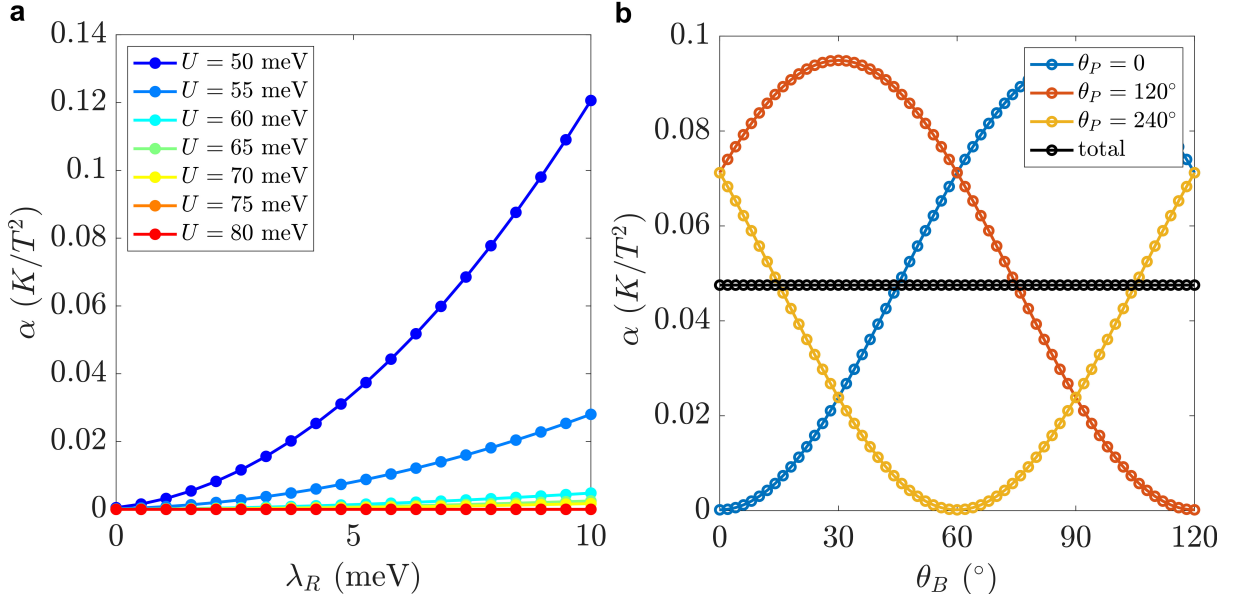
and the function F is given by a series expansion of

$$F \approx \frac{1}{B^2} \int \frac{d^2\mathbf{p}}{(2\pi)^2} \frac{\tanh\left(\frac{\tilde{\epsilon}_{\tau,\mathbf{p}}}{2k_B T_{C,0}}\right) + \tanh\left(\frac{\tilde{\epsilon}_{-\tau,-\mathbf{p}}}{2k_B T_{C,0}}\right)}{\tilde{\epsilon}_{\tau,\mathbf{p}} + \tilde{\epsilon}_{-\tau,-\mathbf{p}}} - \frac{\tanh\left(\frac{\epsilon_{\tau,\mathbf{p}}}{2k_B T_C}\right) + \tanh\left(\frac{\epsilon_{-\tau,-\mathbf{p}}}{2k_B T_C}\right)}{\epsilon_{\tau,\mathbf{p}} + \epsilon_{-\tau,-\mathbf{p}}} \quad (65)$$

in powers of magnetic field B , the leading order of which is independent of B as required. The perturbation can be evaluated in a closed form; however, the resulting expression is not particularly transparent.

Let us now analyze the consequences of the result in Eq.(64) mirroring the analysis of the previous section. SI Fig. 5a shows a plot of numerically determined α coefficient from Eq.(64) as a function of layer potential U and microscopic λ_R for $p_F \sim \sqrt{n}/4 \sim 0.05 \text{ nm}^{-1}$ at $T_{C,0} \approx 100 \text{ mK}$ and $\lambda_I = 1.5 \text{ meV}$. We again see that no realistic value of $\lambda_R \lesssim 10 \text{ meV}$ reproduces the experimental values of $\alpha \sim 0.1 \text{ K}/T^2$ seen in SC_2 for large U values. This again supports our conclusions of the previous depairing analysis and points towards the mechanism of Sec.5 as controlling the resilience to the magnetic field of the SC_2 .

In SI Fig. 5b, we fix $\lambda_R = 2 \text{ meV}$ and $U = 65 \text{ meV}$ and vary the orientation of in-plane magnetic field θ_B . The three curves ($\theta_B = 0, 120^\circ, 240^\circ$) correspond to the expected depairing if only one of



Supplementary Information Fig. 5 | Coefficient α in $T_C = T_{C,0} - \alpha B^2$ in the $\lambda_I \gg E_F$ limit. **a**, Dependence of the coefficient α from Eq.(64) for various potentials U and Rashba coupling λ_R . Here we use $p_F \sim \sqrt{n/4} \sim 0.05 \text{ nm}^{-1}$ at $T_{C,0} \approx 100 \text{ mK}$ and $\lambda_I = 1.5 \text{ meV}$. **b**, Dependence of α on an in-plane B field direction θ_B . Here $U = 65 \text{ meV}$, $\lambda_R = 2 \text{ meV}$. $\theta_P = 0, 120^\circ, 240^\circ$ label the three trigonal warping pockets. See also the discussion in the text.

the three trigonal warping pockets is occupied. When all three pockets are occupied (as in SC_1), there is no dependence on an in-plane B field direction in line with results of Ref. 18. While the precise value of α is controlled by $T_{C,0}$, λ_R and U , we notice that if only one pocket were occupied, then one expects a significant variation in T_C as a function of in-plane B field direction. This contrasts the experiment; see Extended Data Fig. 17, thus suggesting that perhaps a strict “flocking” model is not applicable and the Fermi surface could reconstruct itself in response to the applied B field to minimize depairing - a proposal that can be verified in future self-consistent HF works that allow for nematicity.